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# H8/300H Tiny Series

## User-Mode Flash Memory Reprogramming

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### Introduction

Flash memory reprogramming is performed in user mode using asynchronous serial communication.

### Target Device

H8/3664F

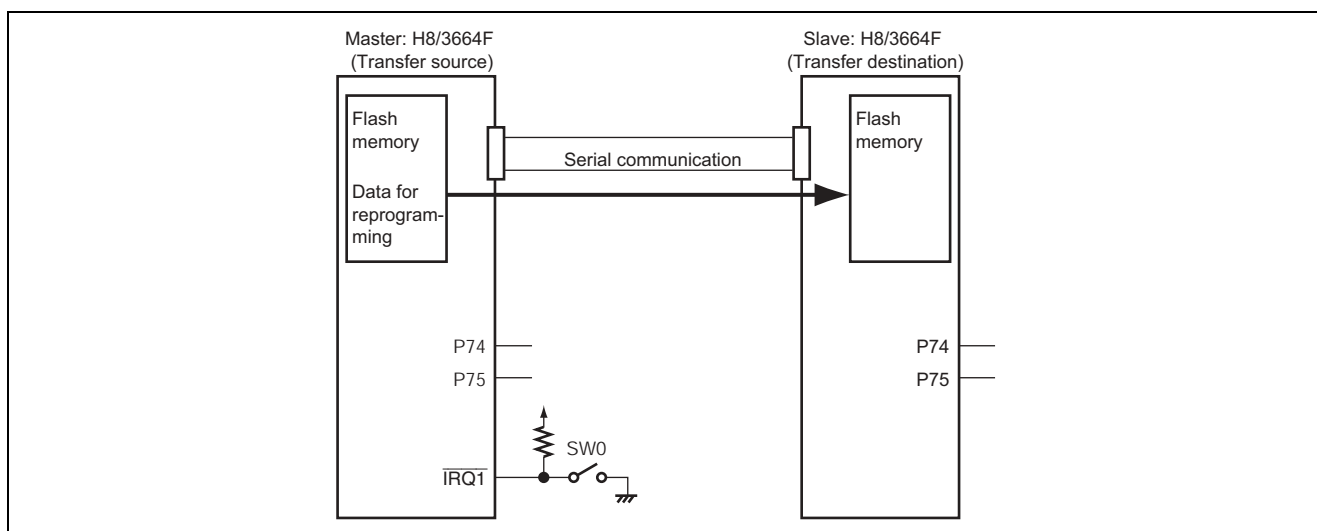
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## 1. Specifications

- Flash memory is reprogrammed in user mode.
- Reprogram data in the flash memory of the master device are programmed into the flash memory of the slave device.
- Reprogram data is transferred by asynchronous serial communications using SCI3.
- Switch 0 (SW0) is connected to the  $\overline{\text{IRQ0}}$  pin of the master device.
- When switch 0 (SW0) of the master is turned on, a flash memory reprogramming start command is sent from the master to the slave and the reprogramming of the slave-side flash memory starts.
- During flash memory reprogramming, P74 is high and P75 is low on both the master and slave; and after the flash memory reprogramming is finished, P74 goes low and P75 goes high.

Figure 1 shows an example configuration of an on-board reprogramming circuit.



**Figure 1 Example Configuration of On-Board Reprogramming Circuit**

### 1.1 On-board Programming Operating Conditions

- CPU operation: User mode
- Operating voltage: 5.0 V
- Operating frequency: 16 MHz

### 1.2 On-Board Programming Mode

- User Mode

It is assumed that a program/erase control program, reprogram-start command reception program, and RAM transfer program have already been programmed into the flash memory of the slave device in boot mode or writer mode.

### 1.3 Programming Method

The flash memory of the slave device is reprogrammed with the reprogram data received from the transfer source.

Communication with the transfer source is performed by asynchronous serial communication using SCI3. The master device is the transfer source, and the slave device is the transfer destination.

### 1.4 Flowchart of Reprogramming Procedure

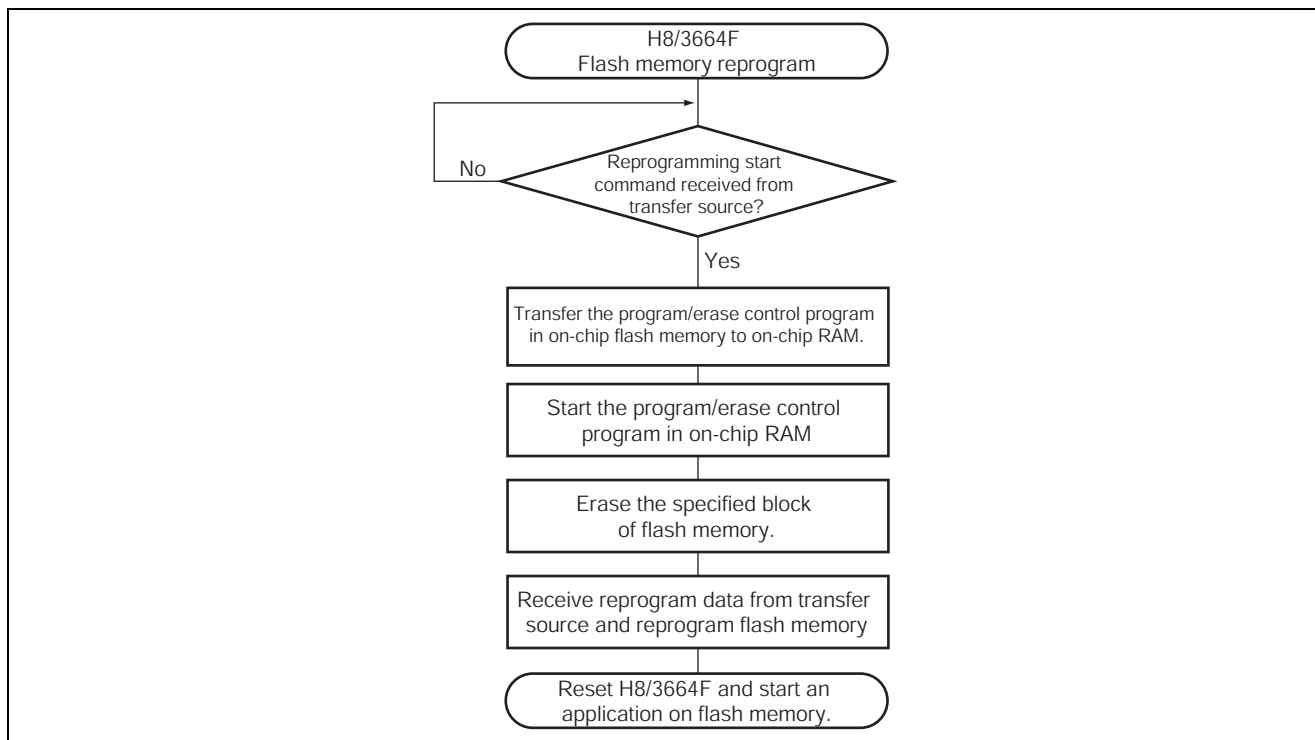


Figure 2 User-Mode Programming Procedure (Slave Device)

### 1.5 Diagram of Master-Slave Connection

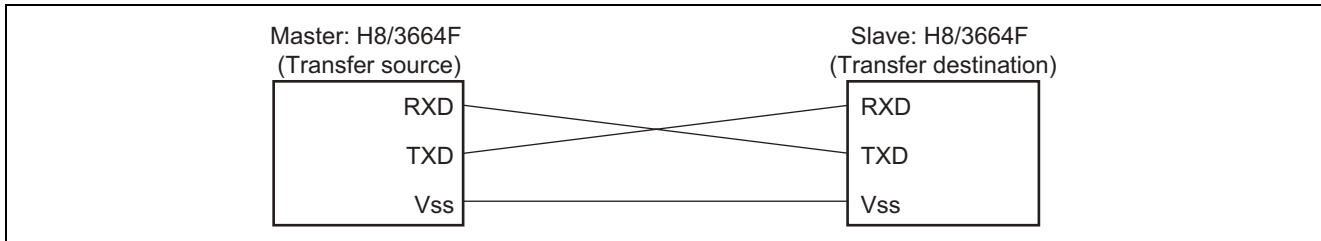


Figure 3 Master-Slave Connection

### 1.6 Communication Specifications

Table 1 Communication Specifications

Item	Setting
Transfer speed	38400 bps
Transfer method	Asynchronous serial communications
Data bits	8
Stop bit	1
Parity	None

### 1.7 Communication Commands

Table 2 Communication Commands

Communication Command	Description
H'00	Normal communication (command name: OK command)
H'01	Communication error (command name: NG command)
H'11	Transmission start request
H'55	Reprogram start command
H'77	Erase command
H'88	Program command

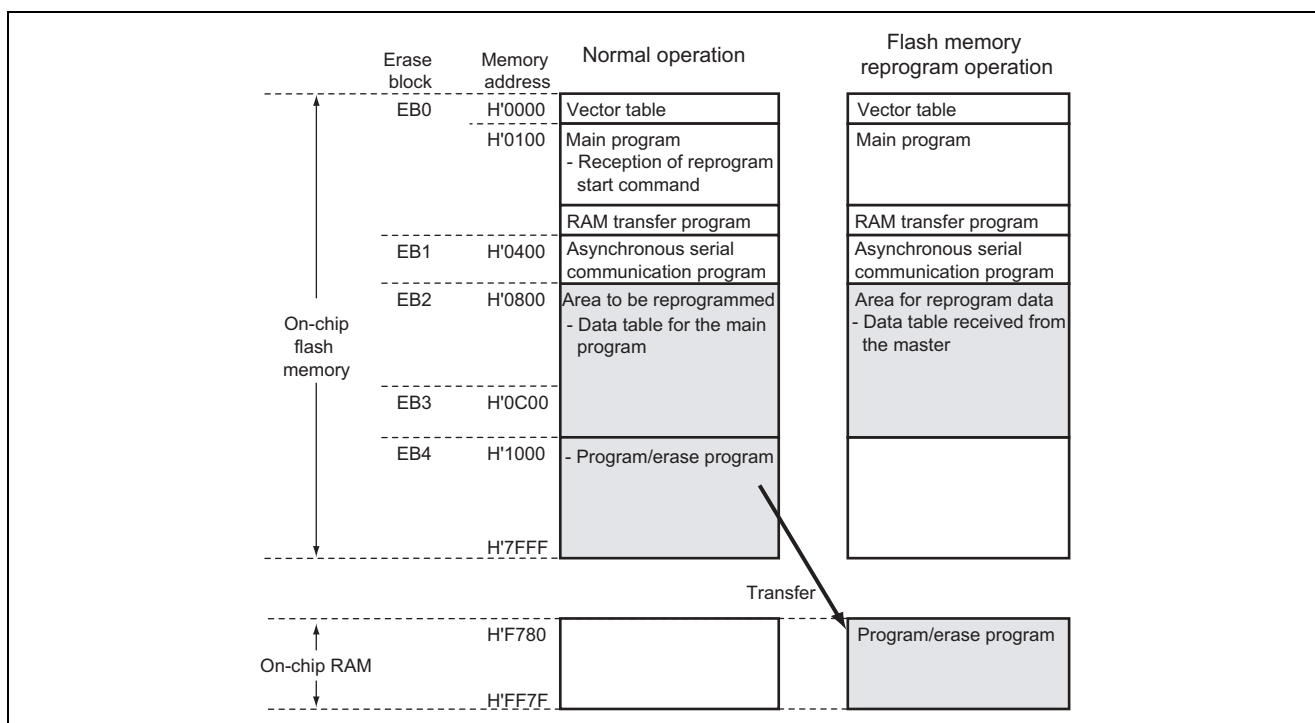
### 1.8 Memory Allocation

Table 3 shows the erase blocks in flash memory of the H8/3664F.

**Table 3 Erase Blocks in Flash Memory**

Block No.	Block (Size)	Address
0	EB0 (1 kbyte)	H'0000 to H'03FF
1	EB1 (1 kbyte)	H'0400 to H'07FF
2	EB2 (1 kbyte)	H'0800 to H'0BFF
3	EB3 (1 kbyte)	H'0C00 to H'0FFF
4	EB4 (28 kbytes)	H'1000 to H'7FFF

Figure 4 shows the memory maps during normal operation of the H8/3664F and during flash memory reprogramming.



**Figure 4 Memory Maps (Slave Device)**

## 2. Description of Functions

### 2.1 Description of Registers

- Flash Memory Control Register 1 (FLMCR1)  
FLMCR1 causes the flash memory to make transitions to program mode, program-verify mode, erase mode, and erase-verify mode.
- Flash Memory Control Register 2 (FLMCR2)  
FLMCR2 indicates the state of reprogramming/erasure of flash memory. FLMCR2 is a read-only register and should not be written to.
- Block Specification Register 1 (EBR1)  
EBR1 specifies an erase block in flash memory. When the SWE bit in FLMCR1 is 0, EBR1 is initialized to H'00. Two or more bits of this register should not be set to 1 at a time. If set, EBR1 will be cleared to 0 automatically.
- Flash Memory Power Control Register (FLPWCR)  
FLPWCR selects whether the flash memory is placed in power-down mode when the LSI enters sub-active mode. In power-down mode, the power supply circuitry is partially stopped, but reading of flash memory is possible.
- Flash Memory Enable Register (FENR)  
FENR controls access to the flash memory control registers FLMCR1, FLMCR2, EBR1, and FLPWCR from the CPU.

### 2.2 Programming and Erasure in User Mode

Also in user mode, a desired block can be erased or reprogrammed on-board by branching to a program/erase program prepared by the user. The branching condition settings and the means for supplying on-board reprogramming data must be prepared by the user. Also, where necessary, a program/erase program or a program for loading the program/erase program from an external source must be programmed into a part of flash memory. Since the flash memory cannot be read during reprogramming or erasure, the program/erase program should be transferred to and executed from on-chip RAM, as is done in boot mode. A program/erase program should be prepared as described in section 2.3, Program/Erase Program.

### 2.3 Program/Erase Program

On-board flash memory programming and erasure are implemented by software using the CPU. The flash memory enters program mode, program-verify mode, erase mode, or erase-verify mode according to the setting of FLMCR1. A boot-mode program control program and user-mode program/erase program perform programming and erasure by combining the above modes. Flash memory should be programmed and erased in accordance with the following notes on "program/program-verify" and "erase/erase-verify", respectively.

- **Program/Program-Verify**

- (1) Programming must be performed on the erased part of flash memory; do not program the addresses that have already been programmed.
- (2) Programming should be performed in 128-byte units. Even when data less than 128 bytes are to be programmed, it is necessary to transfer 128 bytes of data to the flash memory. Addresses for which there is no data for programming should be programmed with H'FF.
- (3) The following data storage areas should be allocated in RAM: a 128-byte programming data area, a 128-byte reprogramming data area, and a 128-byte additional programming data area. Computation of reprogramming data and additional programming data should be as shown in tables 4 and 5, respectively.
- (4) 128 bytes of data should be transferred continuously in byte units from the reprogramming data area or additional programming data area to the flash memory. The program address and 128 bytes of data are latched in the flash memory. The lower 8 bits of the first address of the transfer destination area in the flash memory should be either H'00 or H'80.
- (5) The time during which the P bit is set is the programming time. Programming times are as shown in table 6.
- (6) The watchdog timer is set to prevent excessive programming resulting from program runaway or other causes. The overflow period should be set to approx. 6.6 ms.
- (7) For a dummy write to a verify address, one byte data, H'FF, should be written to an address whose lowermost bit is B'0. The verify data is read as a word from the address to which a dummy write was performed.
- (8) The program/program-verify sequence should not be repeated more than 1000 times for the same bit.

**Table 4 Reprogramming Data Computation**

Programmed Data	Result of Verification	Reprogramming Data	Remarks
0	0	1	Programming completed
0	1	0	Bit requires reprogramming
1	0	1	—
1	1	1	Remains in an erased state.

**Table 5 Additional Programming Data Computation**

Reprogramming Data	Result of Verification	Additional Programming Data	Remarks
0	0	0	Bit requires additional programming
0	1	1	Additional programming is not required.
1	0	1	Additional programming is not required.
1	1	1	Additional programming is not required.

**Table 6 Programming Time**

n (Number of Programming Operations)	Programming	Additional Programming	Remarks
1 to 6	30 [ $\mu$ s]	10 [ $\mu$ s]	—
7 to 1000	200 [ $\mu$ s]	—	—

- **Erase/Erase-Verify**

- (1) There is no need to pre-write (setting erase block data to all 0) prior to erasure.
- (2) Erasure is performed in block units. Only one erase block should be selected using the block specification register 1 (EBR1). Even when multiple blocks are to be erased, they must be erased in sequence one block at a time.
- (3) The time during which the E bit is set is the erase time.
- (4) The watchdog timer is set to prevent excessive erasure resulting from program runaway or other causes. The overflow period should be set to approx. 19.8 ms.
- (5) For a dummy write to a verify address, one byte of H'FF should be written to an address whose lowermost bit is B'0. The verify data is read as a word from the address to which a dummy write was performed.
- (6) If the read data is found to have not been erased, erase mode should be set again, and the erase/erase-verify sequence should be repeated in the same way. However, the number of repetitions should not exceed 100.

- **Interrupts During Programming/Erasure of Flash Memory**

During flash memory programming/erasure or execution of the program/erase control program, all interrupt requests, including NMI, should be disabled for the following reason.

- (1) If an interrupt occurs during programming/erasure, operation conforming to the normal program/erase algorithm cannot be guaranteed.

## 3. Description of Operation

### 3.1 Normal Operation

1. The normal application normally accesses a data table in flash memory; the data table is received from the master and reprogrammed.
2. In the flash memory of the slave device, a program/erase control program, reprogram-start command reception program, and RAM transfer program must be programmed in advance.
3. Data communication between master and slave is performed by asynchronous serial communications using SCI3.

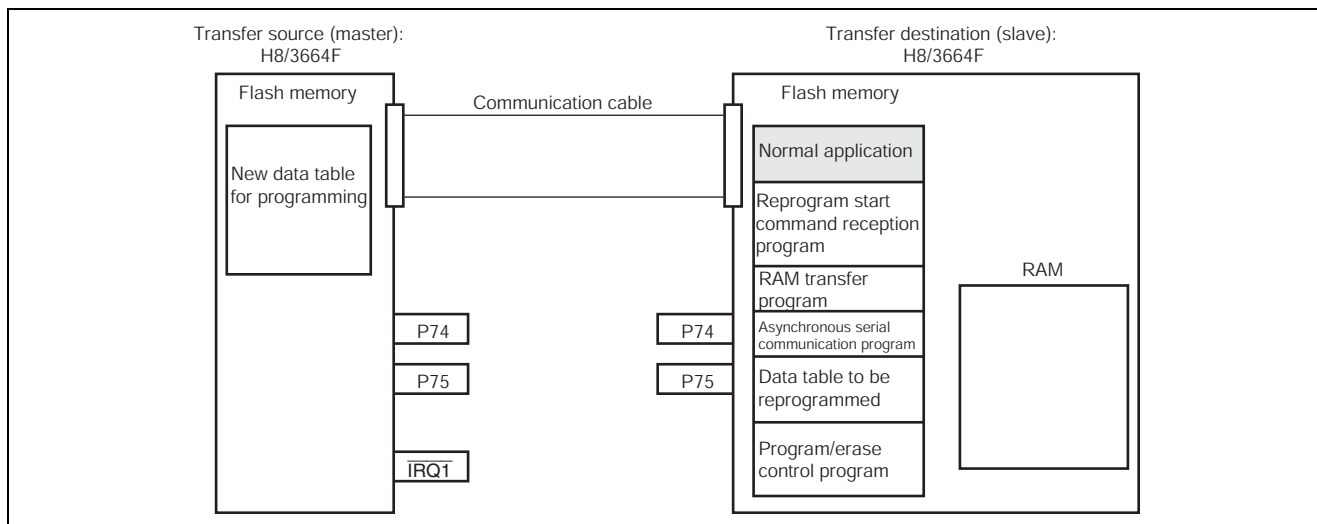


Figure 5 Normal Operation

### 3.2 Preparations for On-board Reprogramming

1. When a falling edge is detected on the master's  $\overline{\text{IRQ1}}$  pin, the master sends a reprogram start command H'55.
2. At this time on the master device, P74 is high and P75 is low.

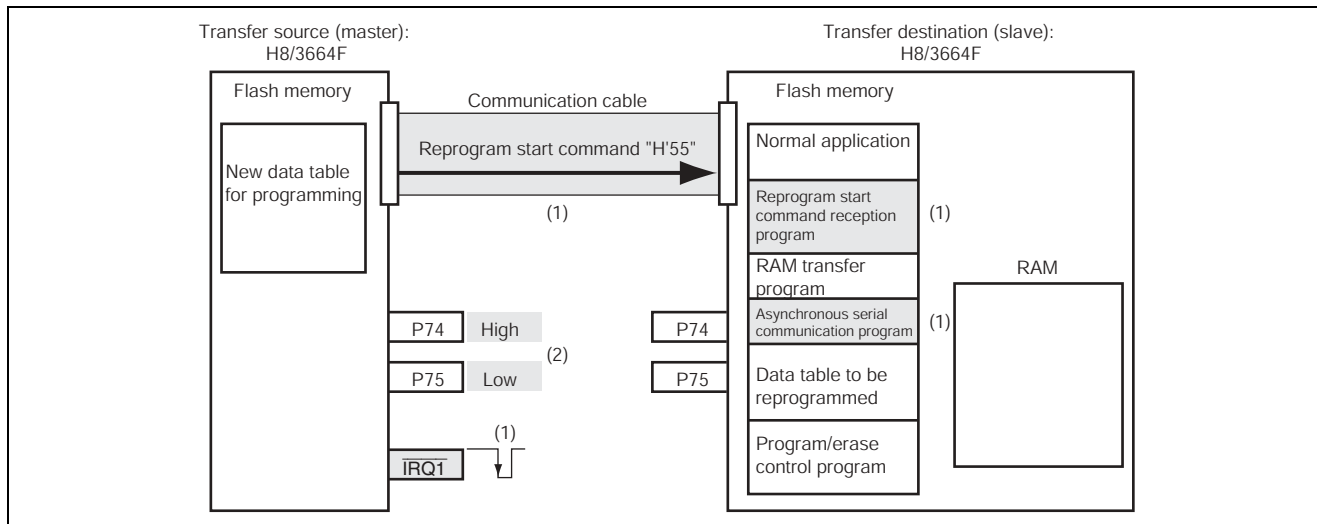


Figure 6 Preparations for On-board Reprogramming

### 3.3 Starting On-Board Reprogramming

1. On receiving the command H'55, the slave device starts the RAM transfer program, and transfers the program/erase control program to the on-chip RAM.
2. At this time on the slave device, P74 is high and P75 is low.

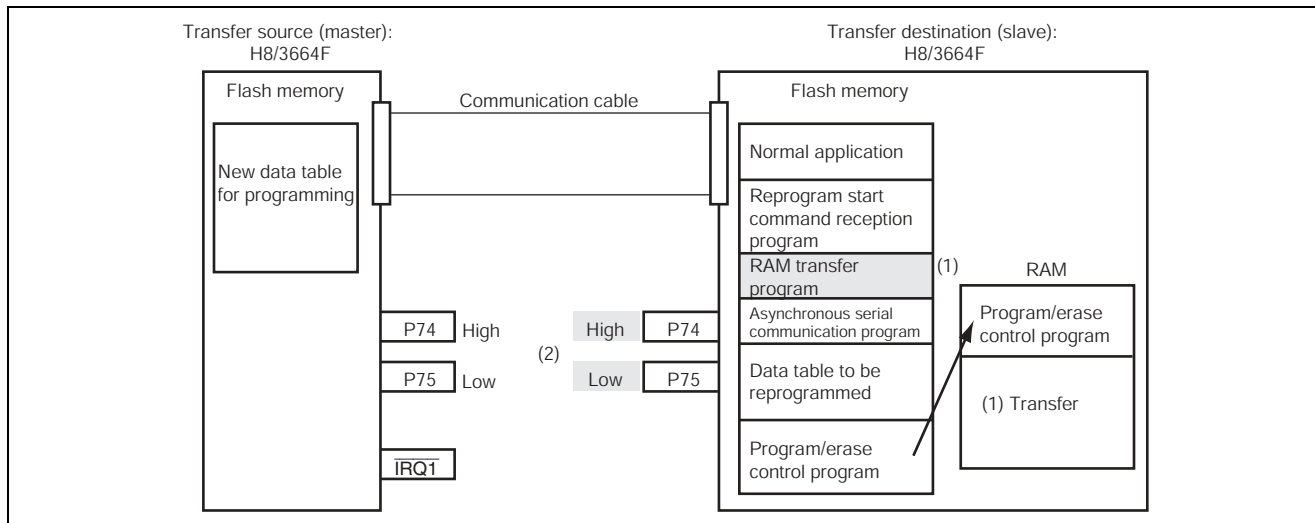


Figure 7 Starting On-Board Reprogramming

### 3.4 Running the Program/Erase Control Program

1. After the transfer by the RAM transfer program has ended, execution branches to the program/erase control program in RAM.

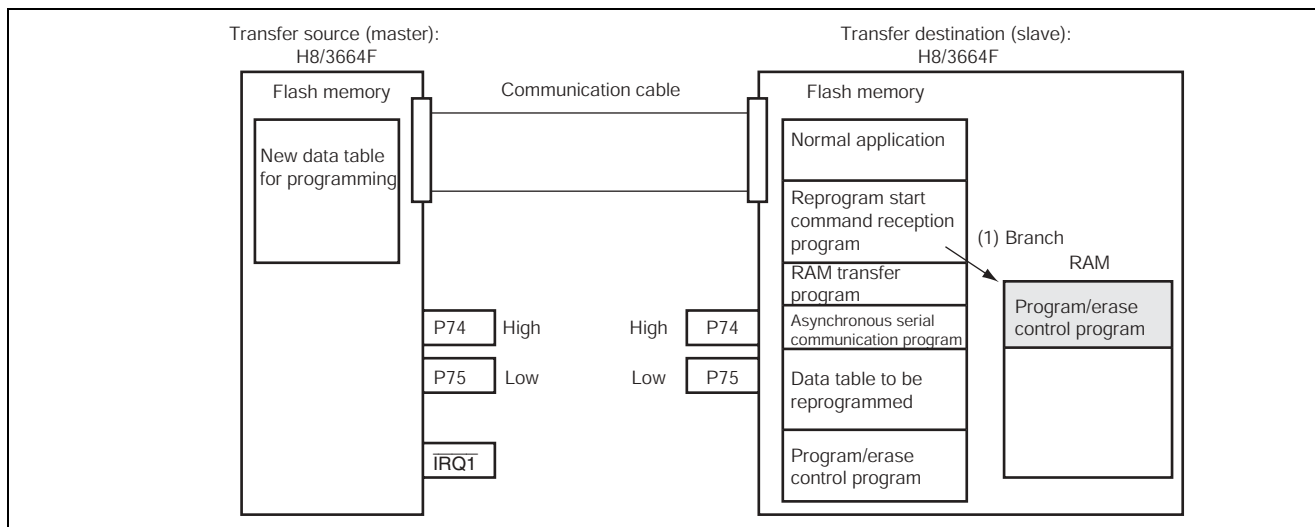


Figure 8 Running the Program/Erase Control Program

### 3.5 Flash Memory Erasure

1. The slave receives an erase command H'77 from the master.
2. The program/erase control program erases the specified block of the flash memory.

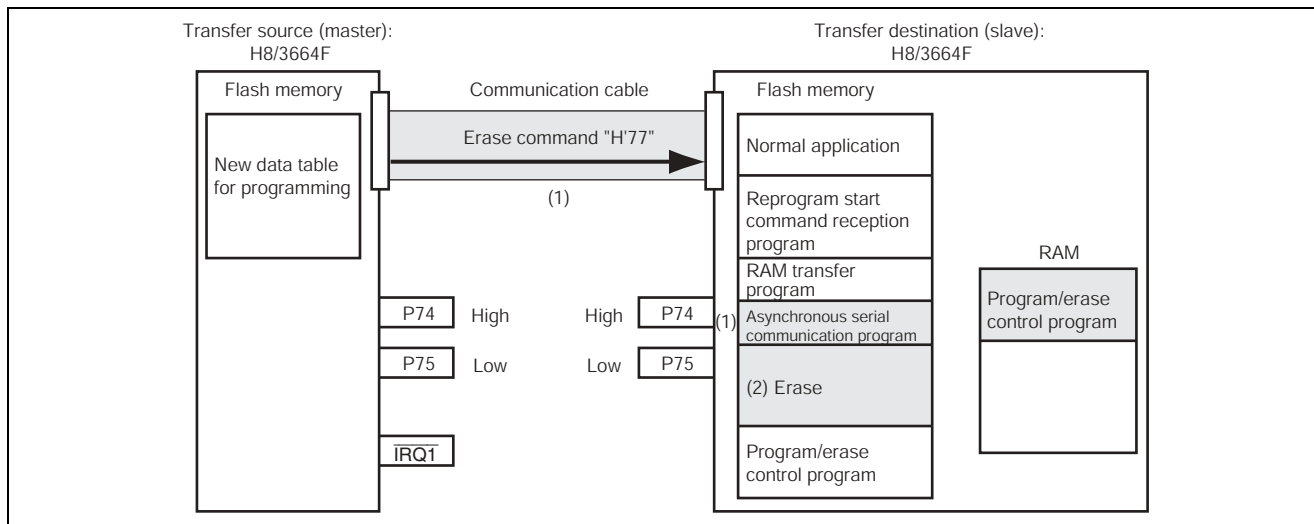


Figure 9 Flash Memory Erasure

### 3.6 Flash Memory Programming

1. The slave receives a program command H'88 from the master.
2. The program/erase control program receives a new data table from the master, and programs it into the flash memory.
3. After the programming is finished, P74 is low and P75 is high for both master and slave.

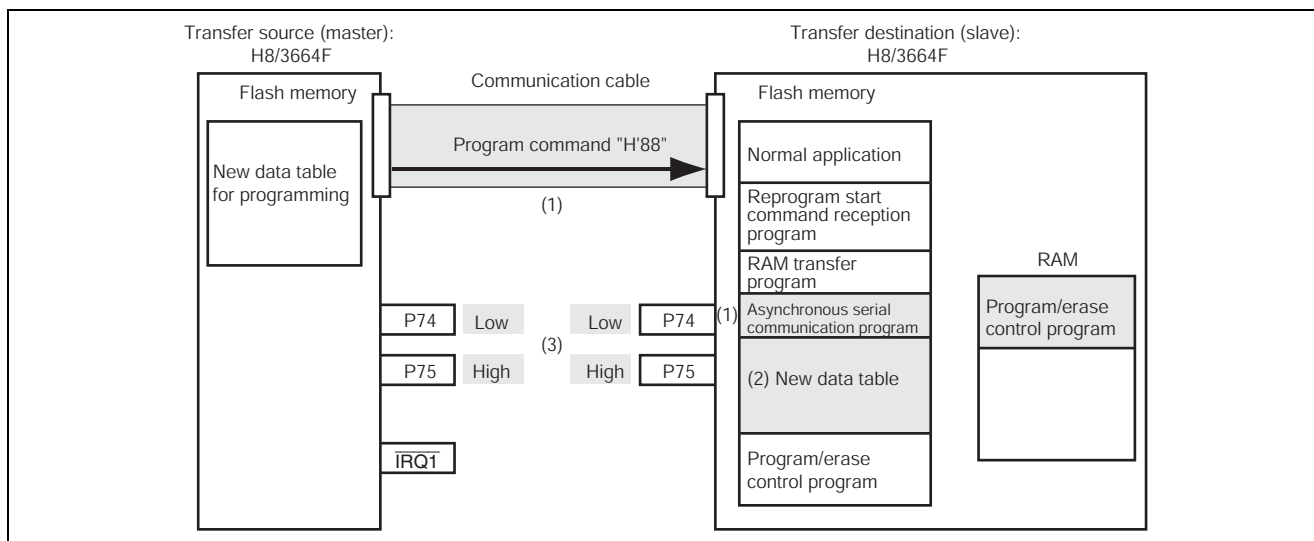
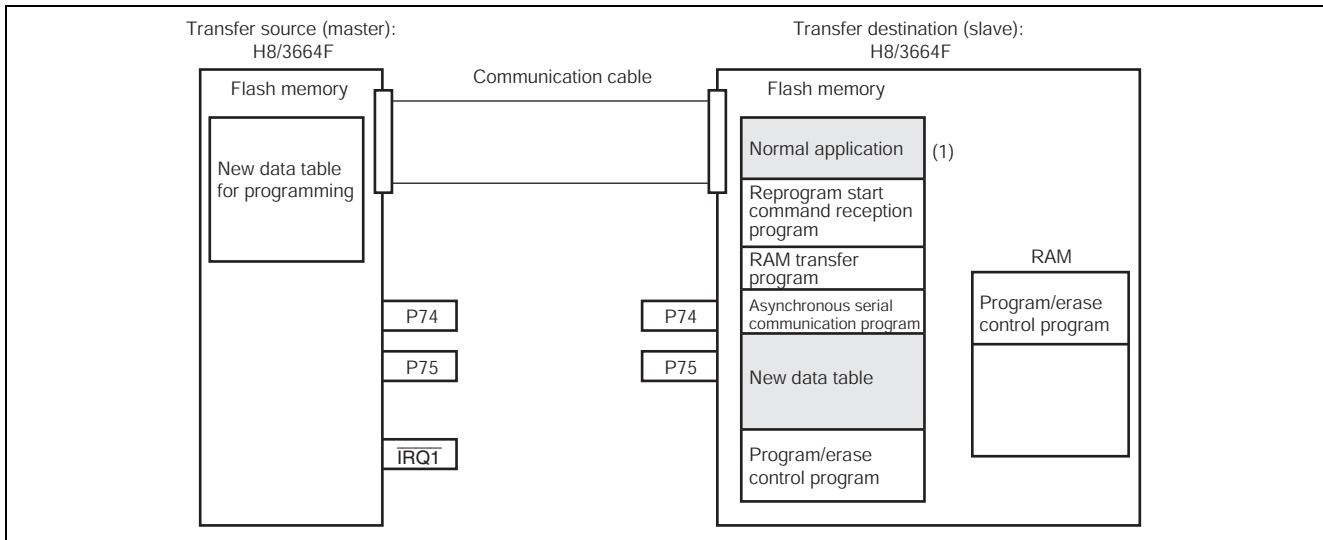


Figure 10 Flash Memory Programming

**3.7 Running the Normal Application Program**

1. The slave H8/3664F is reset, and the normal application that accesses the new data table is started.



**Figure 11 Running the Normal Application Program**

4. Sequence Diagrams

4.1 Normal Operation

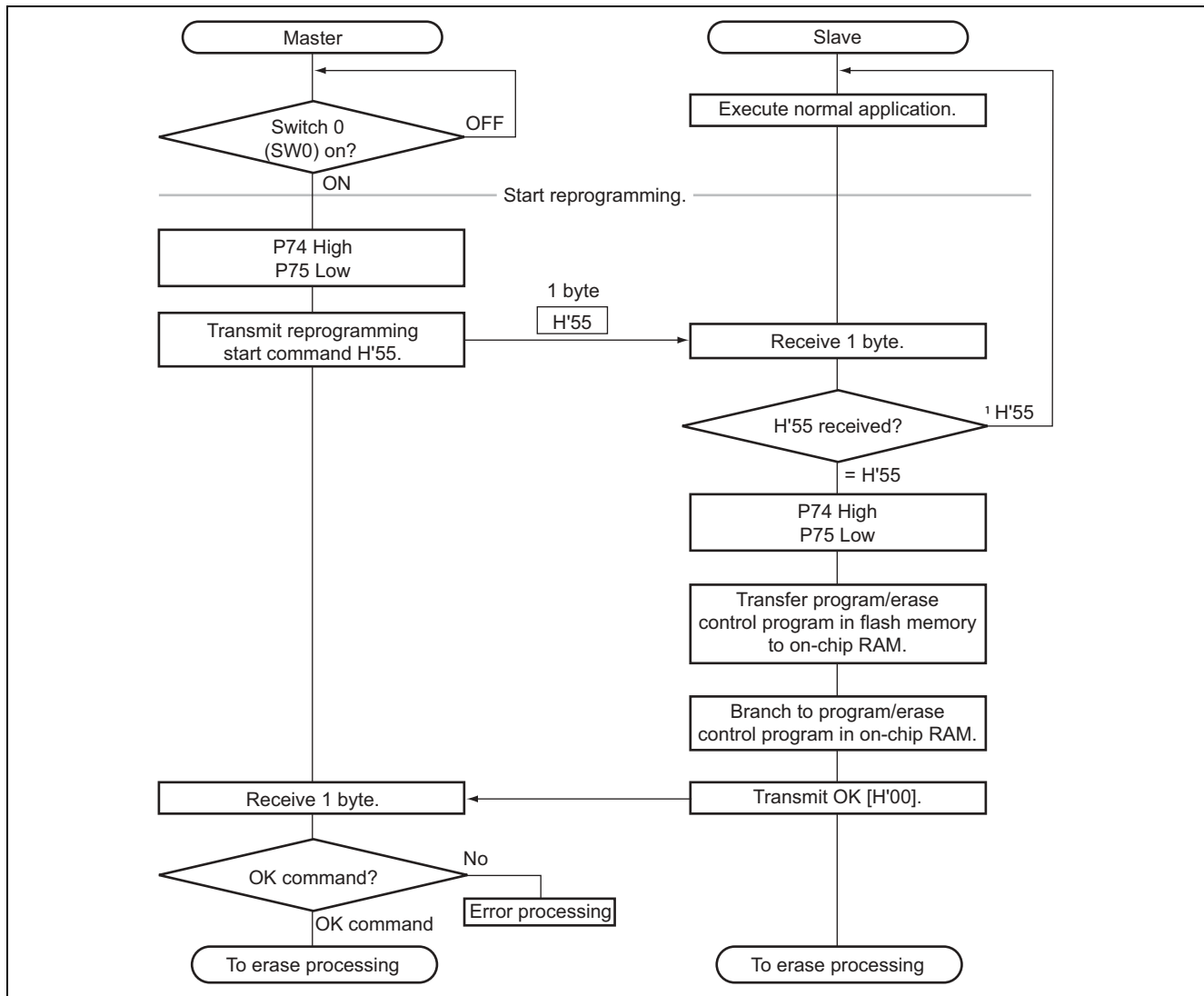


Figure 12 Normal Operation

4.2 Erase Processing

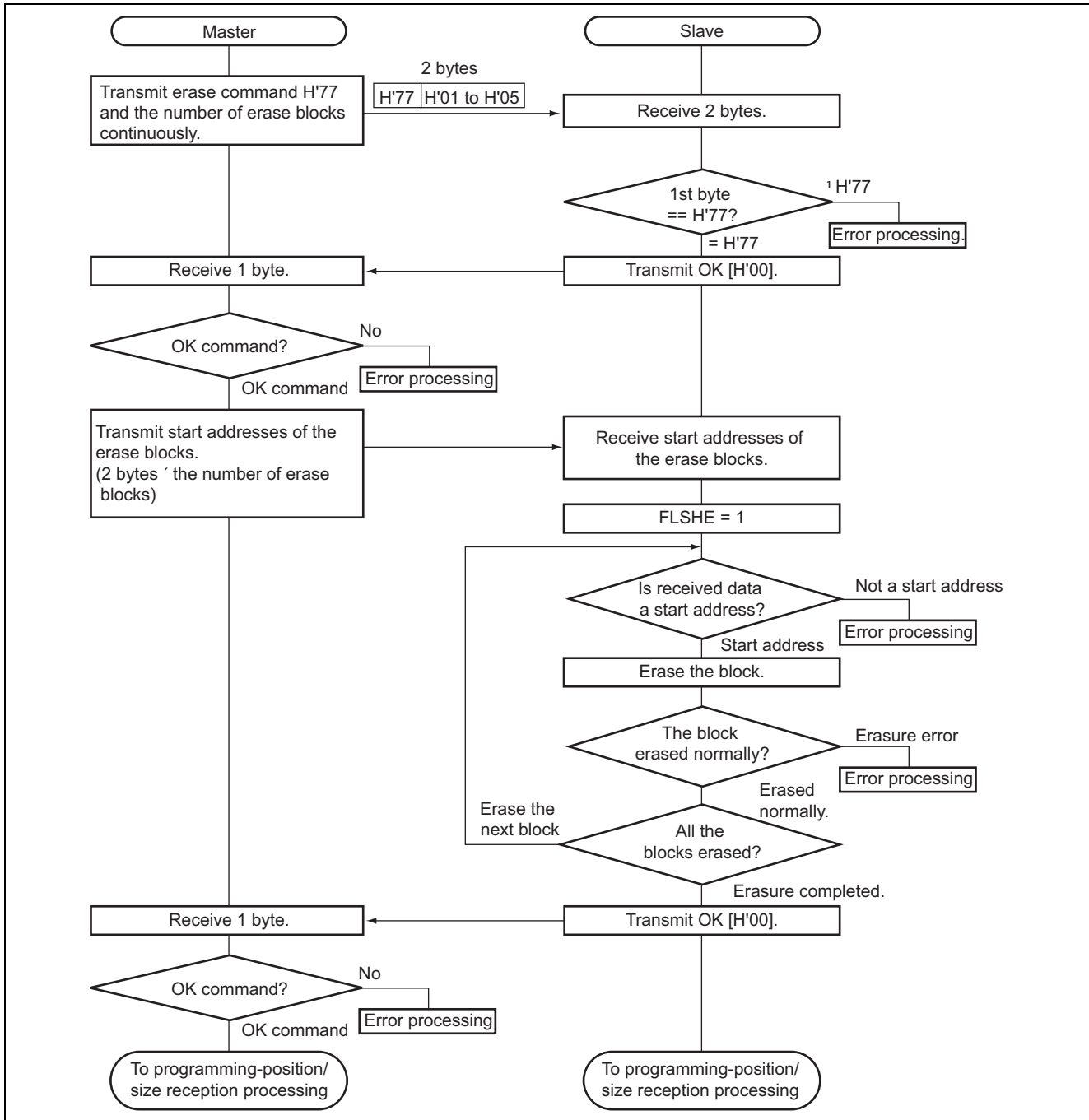


Figure 13 Erase Processing

4.3 Programming Position/Size Reception Processing

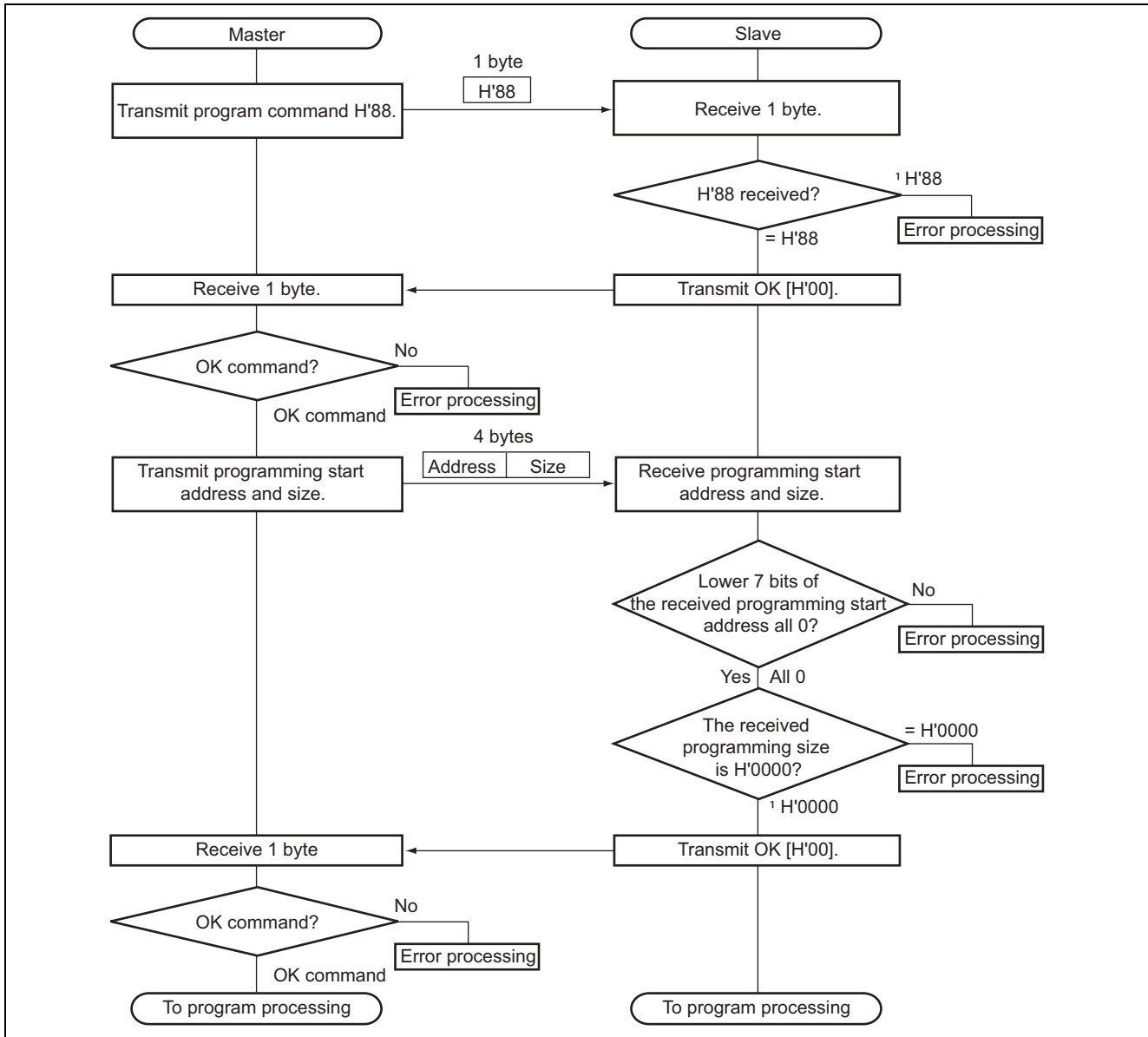


Figure 14 Programming Position/Size Reception Processing

4.4 Program Processing

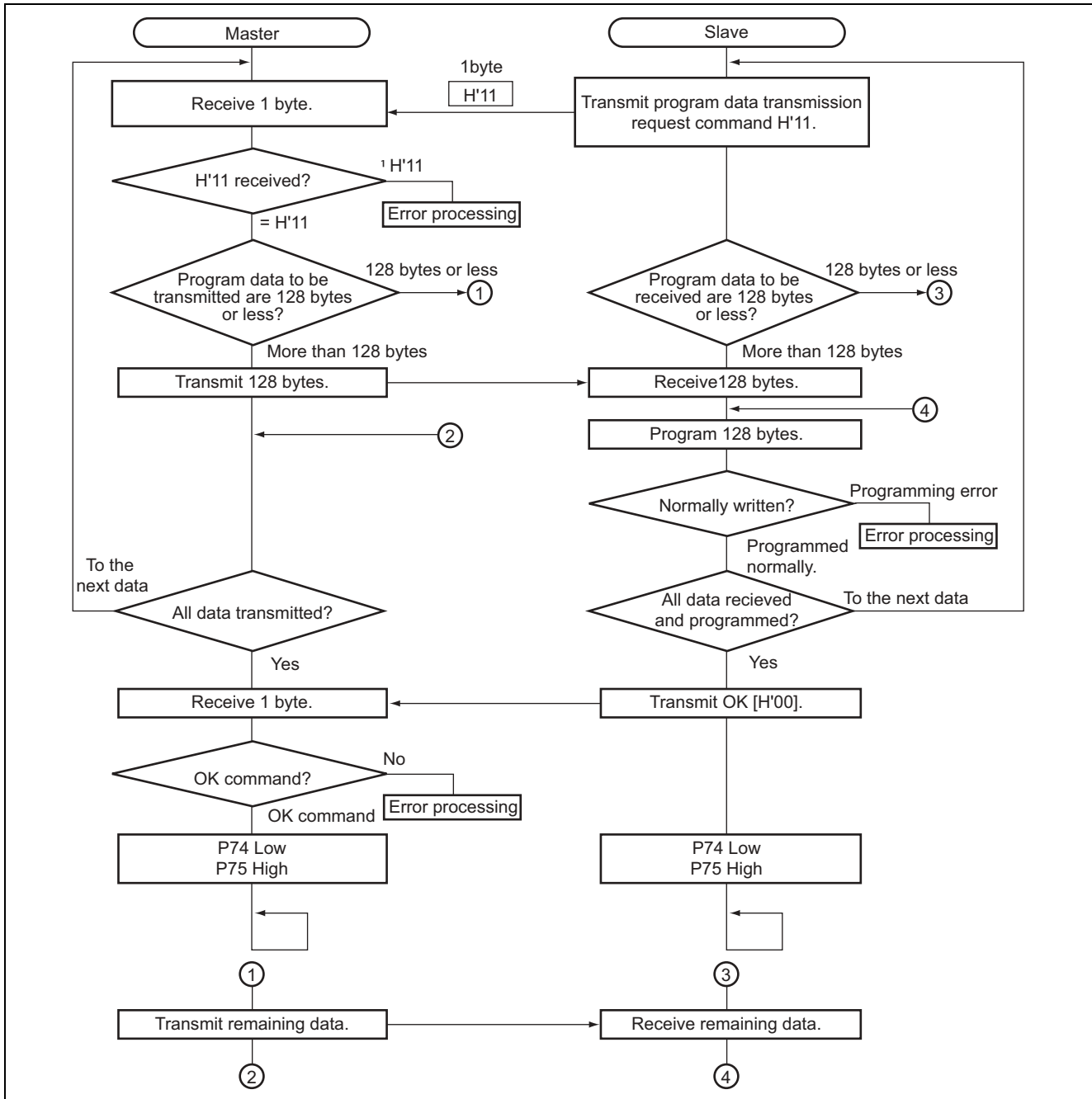
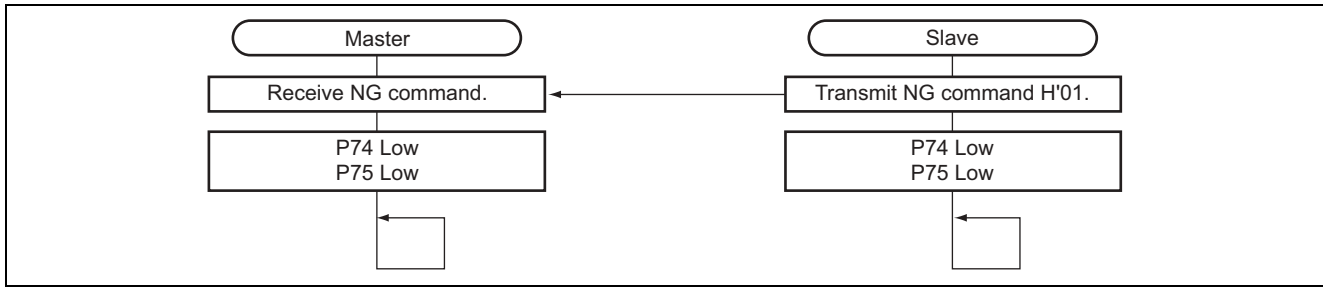


Figure 15 Program Processing

**4.5 Error Processing**



**Figure 16 Error Processing**

## 5. Slave-Side Normal Program

### 5.1 Hierarchical Structure

The slave-side normal program that runs in flash memory (slave-side normal program) performs processing to execute a user application program (normal application), receive the reprogramming start command, and transfer the program/erase control program in flash memory to on-chip RAM. The hierarchical structure of routines used in the slave-side normal program is shown in figure 17.

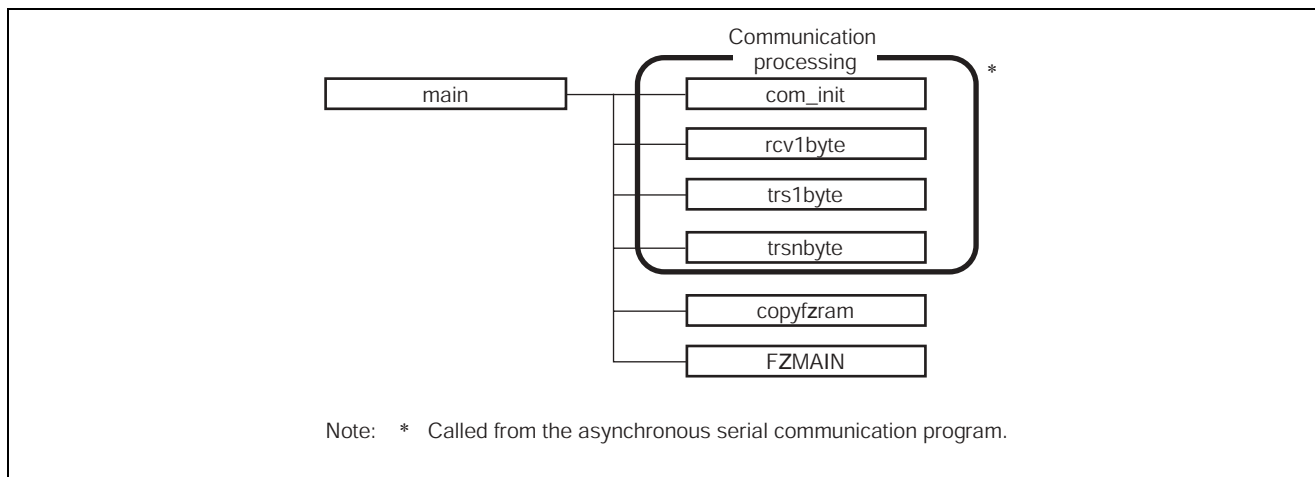


Figure 17 Slave-Side Normal Program

### 5.2 List of Functions

Table 7 Functions of Slave-Side Normal Program

Function Name	Description
main	Executes the normal application, receives a reprogramming start command, and transfers the program/erase control program in flash memory to on-chip RAM.
copyfzram	Transfers the flash memory program/erase control program to RAM.
FZMAIN	Flash memory program/erase control program

### 5.3 Modules

#### 5.3.1 main() Function

(1) Module Specifications

- Functional summary
  - Executes the user application program (normal application)
  - Performs reprogramming-start command reception processing
  - Branches to the program/erase control program

Table 8 Module Specifications

	Type	Variable Name	Description
Argument	None	None	None

### (2) Internal Registers

The following describes internal registers used in this sample task

- SSR: Serial status register (Address: H'FFAC)

Bit	Bit Name	Setting	Description
6	RDRF	Undefined	Receive Data Register Full 0: No receive data is stored in RDR. 1: Receive data is stored in RDR.

- PDR7: Port data register 7 (Address: H'FFDA)

Bit	Bit Name	Setting	Description
5	P75	0	Port 75 0: The P75 pin is low. 1: The P75 pin is high.
4	P74	Undefined	Port 74 0: The P74 pin is low. 1: The P74 pin is high.

- PMR1: Port mode register 1 (Address: H'FFE0)

Bit	Bit Name	Setting	Description
5	IRQ1	1	P15/ $\overline{\text{IRQ1}}$ Pin Function Switching 0: P15/ $\overline{\text{IRQ1}}$ pin functions as a general I/O port. 1: P15/ $\overline{\text{IRQ1}}$ pin functions as the $\overline{\text{IRQ1}}$ input pin.

- PCR7: Port control register 7 (Address: H'FFEA)

Bit	Bit Name	Setting	Description
5	PCR75	0	0: The P75 pin is set up as an input pin. 1: The P75 pin is set up as an output pin.
4	PCR74	0	0: The P74 pin is set up as an input pin. 1: The P74 pin is set up as an output pin.

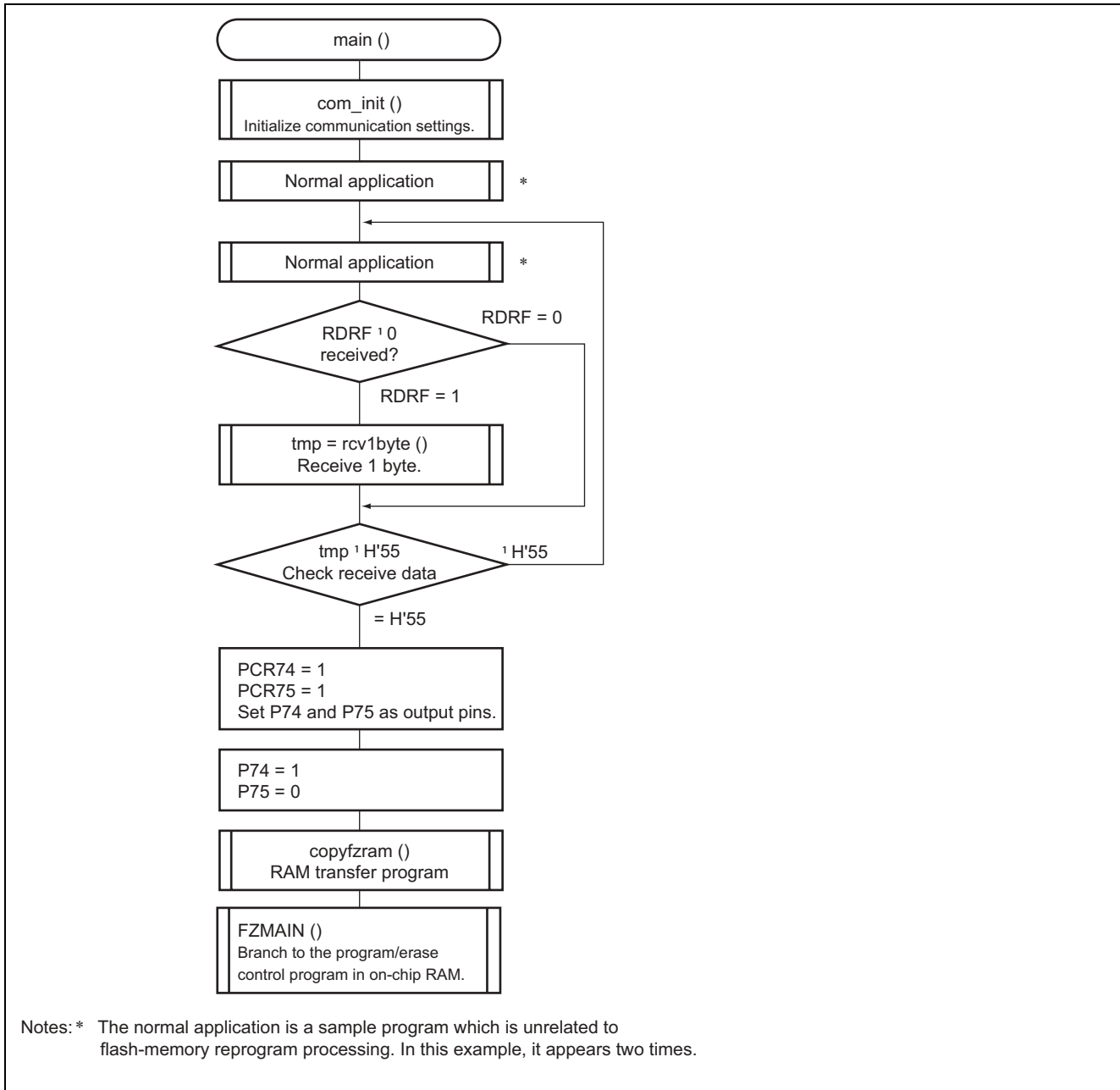
- IEGR1: Interrupt edge select register 1 (Address: H'FFF2)

Bit	Bit Name	Setting	Description
1	IEG1	1	IRQ1 Edge Select 0: The falling edge on the $\overline{\text{IRQ1}}$ pin input is detected. 1: The rising edge on the $\overline{\text{IRQ1}}$ pin input is detected.

- IRR1: Interrupt flag register 1 (Address: H'FFF6)

Bit	Bit Name	Setting	Description
1	IRRI1	0	IRQ1 Interrupt Request Flag 0: An interrupt of the $\overline{\text{IRQ1}}$ pin has not been requested. 1: An interrupt of the $\overline{\text{IRQ1}}$ pin has been requested.

### (3) Flowchart



### 5.3.2 copyfzram() Function

#### (1) Module Specifications

- Functional summary
  - Transfers the flash memory program/erase control program to RAM.

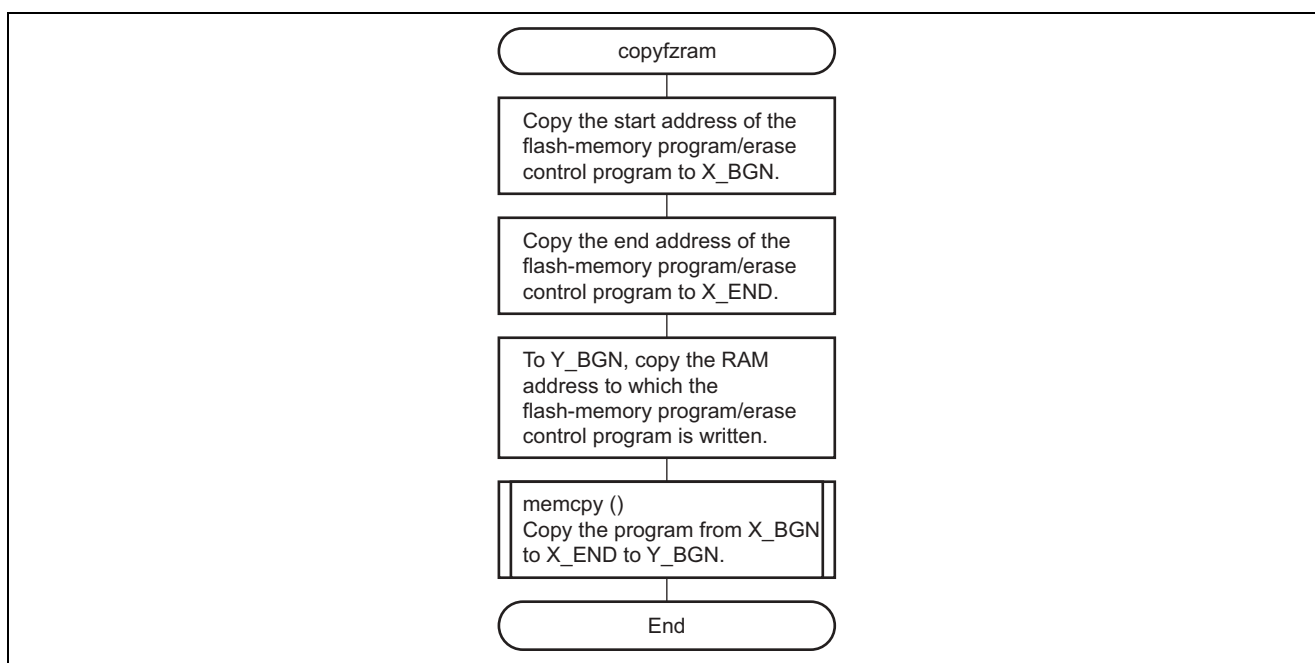
**Table 9 Module Specifications**

	Type	Variable Name	Description
Argument	None	None	None

#### (2) Internal Registers

None

#### (3) Flowchart



### 5.3.3 FZMAIN() Function

#### (1) Module Specifications

- Functional summary
  - Calls the main routine of the program/erase control program.

## 6. Slave-Side Program/Erase Control Program

### 6.1 Hierarchical Structure

The program/erase control program performs erasure in erase block units, receives data to be programmed into flash memory, and programs them into flash memory. Figure 18 shows the hierarchical structure of the routines used in the program/erase control program. Subroutines other than the FZMAIN() function are divided into communication processing and flash memory program/erase processing.

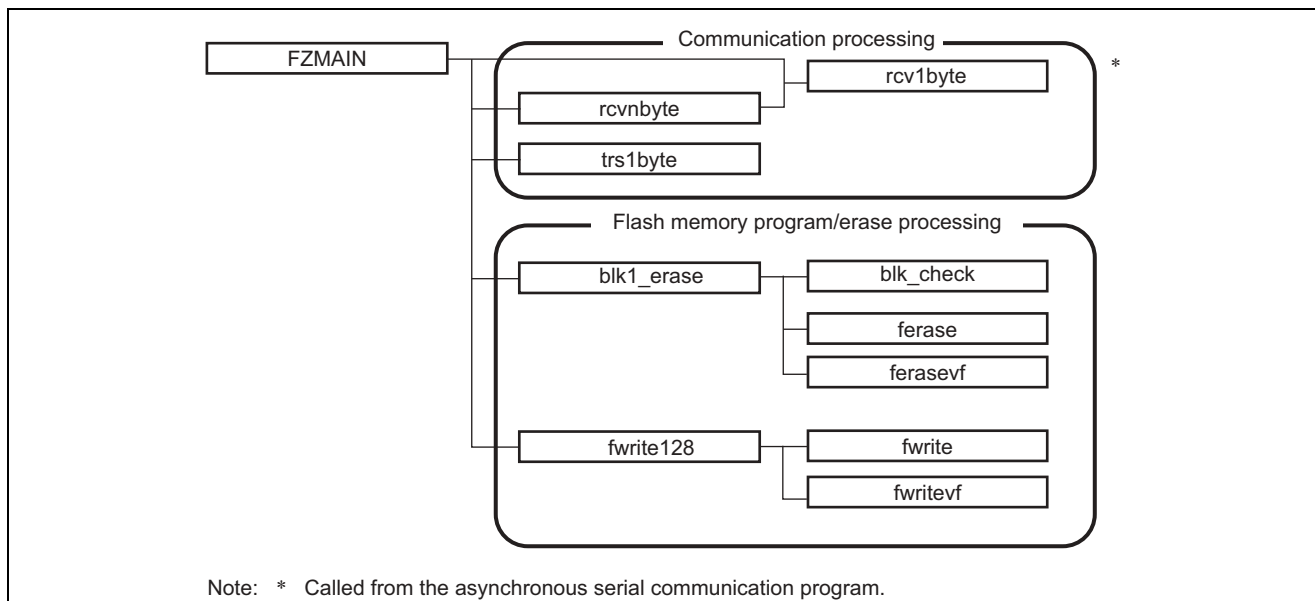


Figure 18 Program/Erase Control Program

### 6.2 List of Functions

Table 10 Functions of Program/Erase Control Program

Function Name	Description
FZMAIN	Main routine of the program/erase control program
blk1_erase	Erases the specified block in the flash memory.
blk_check	Determines the block number of the erase block from the erase start address.
ferase	Erases the specified block.
ferasevf	Erases the specified block and performs verification.
fwrite128	Programs and verifies 128 bytes.
fwrite	Programs data to the specified address.
fwritevf	Verifies data for the specified address and creates reprogramming data.

### 6.3 List of Constants

Table 11 List of Constants

Constant Name	Value	Description
OK	H'00	Return value when normal
NG	H'01	Return value when an error has occurred
WNG	H'02	Programming error
MAXBLK	H'05	Total number of blocks in flash memory
OW_COUNT	H'06	Number of reprogramming operations
WDT_ERASE	H'A0	Watchdog timer setting value for erasure
WDT_WRITE	H'F0	Watchdog timer setting value for programming
WLOOP1	$1 * \text{MHZ} / \text{KEISU} + 1 = 2$ (H'02)	Number of WAIT statement executions, 1- $\mu$ s wait
WLOOP2	$2 * \text{MHZ} / \text{KEISU} + 1 = 4$ (H'04)	Number of WAIT statement executions, 2- $\mu$ s wait
WLOOP4	$4 * \text{MHZ} / \text{KEISU} + 1 = 7$ (H'07)	Number of WAIT statement executions, 4- $\mu$ s wait
WLOOP5	$5 * \text{MHZ} / \text{KEISU} + 1 = 9$ (H'09)	Number of WAIT statement executions, 5- $\mu$ s wait
WLOOP10	$10 * \text{MHZ} / \text{KEISU} + 1 = 17$ (H'11)	Number of WAIT statement executions, 10- $\mu$ s wait
WLOOP20	$20 * \text{MHZ} / \text{KEISU} + 1 = 33$ (H'21)	Number of WAIT statement executions, 20- $\mu$ s wait
WLOOP50	$50 * \text{MHZ} / \text{KEISU} + 1 = 81$ (H'51)	Number of WAIT statement executions, 50- $\mu$ s wait
WLOOP100	$100 * \text{MHZ} / \text{KEISU} + 1 = 161$ (H'A1)	Number of WAIT statement executions, 100- $\mu$ s wait
TIME10	$10 * \text{MHZ} / \text{KEISU} + 1 = 17$ (H'11)	Number of WAIT statement executions, 10- $\mu$ s wait
TIME30	$30 * \text{MHZ} / \text{KEISU} + 1 = 49$ (H'31)	Number of WAIT statement executions, 30- $\mu$ s wait
TIME200	$200 * \text{MHZ} / \text{KEISU} + 1 = 321$ (H'141)	Number of WAIT statement executions, 200- $\mu$ s wait
TIME10000	$10000 * \text{MHZ} / \text{KEISU} + 1 = 16001$ (H'3E81)	Number of WAIT statement executions, 10-ms wait

Note: \* MHZ: 16 (Operating frequency is 16 MHz.)  
KEISU: 10 (The number of steps in one loop when the loop is repeated by a 'for' statement for an unsigned short variable.)

### 6.4 RAM Usage

During execution of the FZMAIN function, the stack memory of table 12 is used. Stack memory is used for program execution, but the amount used varies depending on the compiler version and option settings.

Table 12 RAM Used Mainly

Data Name	Amount Used in Stack Memory
Programming data	128 bytes
Reprogramming data	128 bytes
Additional programming data	128 bytes

## 6.5 Modules

### 6.5.1 FZMAIN() Function

#### (1) Module Specifications

- Functional summary
  - Erases flash memory.
  - Receives data to be programmed into flash memory.
  - Programs data into flash memory.
  - Executes a reset-start after programming is complete.

**Table 12 Module Specifications**

	Type	Variable Name	Description
Argument	None	None	None

#### (2) Internal Registers

- FENR: Flash memory enable register 7 (Address: H'FF9B)

Bit	Bit Name	Setting	Description
7	FLSHE	1	Flash Memory Control Register Enable 0: Disables access to the flash memory control register. 1: Enables access to the flash memory control register.

- TCSRWD: Timer control/status register WD (Address: H'FFC0)

Bit	Bit Name	Setting	Description
7	B6WI	0	Bit 6 Write Disable 0: Enables writing to bit 6 in TCSRWD. 1: Disables writing to bit 6 in TCSRWD.
6	TCWE	1	Timer Counter WD Write Enable 0: Disables writing 8-bit data to TCWD. 1: Enables writing 8-bit data to TCWD.
5	B4WI	0	Bit 4 Write Disable 0: Enables writing to bit 4 in TCSRWD. 1: Disables writing to bit 4 in TCSRWD.
4	TCSRWE	1	Timer Control/Status Register WD Write Enable 0: Disables writing to bit 2 and bit 0 in TCSRWD. 1: Enables writing to bit 2 and bit 0 in TCSRWD.
3	B2WI	0	Bit 2 Write Disable 0: Enables writing to bit 2 in TCSRWD. 1: Disables writing to bit 2 in TCSRWD.
2	WDON	0	Watchdog Timer On 0: Disables watchdog timer operation. 1: Enables watchdog timer operation.
1	B0WI	0	Bit 0 Write Disable 0: Enables writing to bit 0 in TCSRWD. 1: Disables writing to bit 0 in TCSRWD.

Bit	Bit Name	Setting	Description
0	WRST	0	Watchdog Timer Reset 0: Indicates that TCWD has not overflowed and an internal reset signal has not been generated. 1: Indicates that TCWD has overflowed and an internal reset signal has been generated.

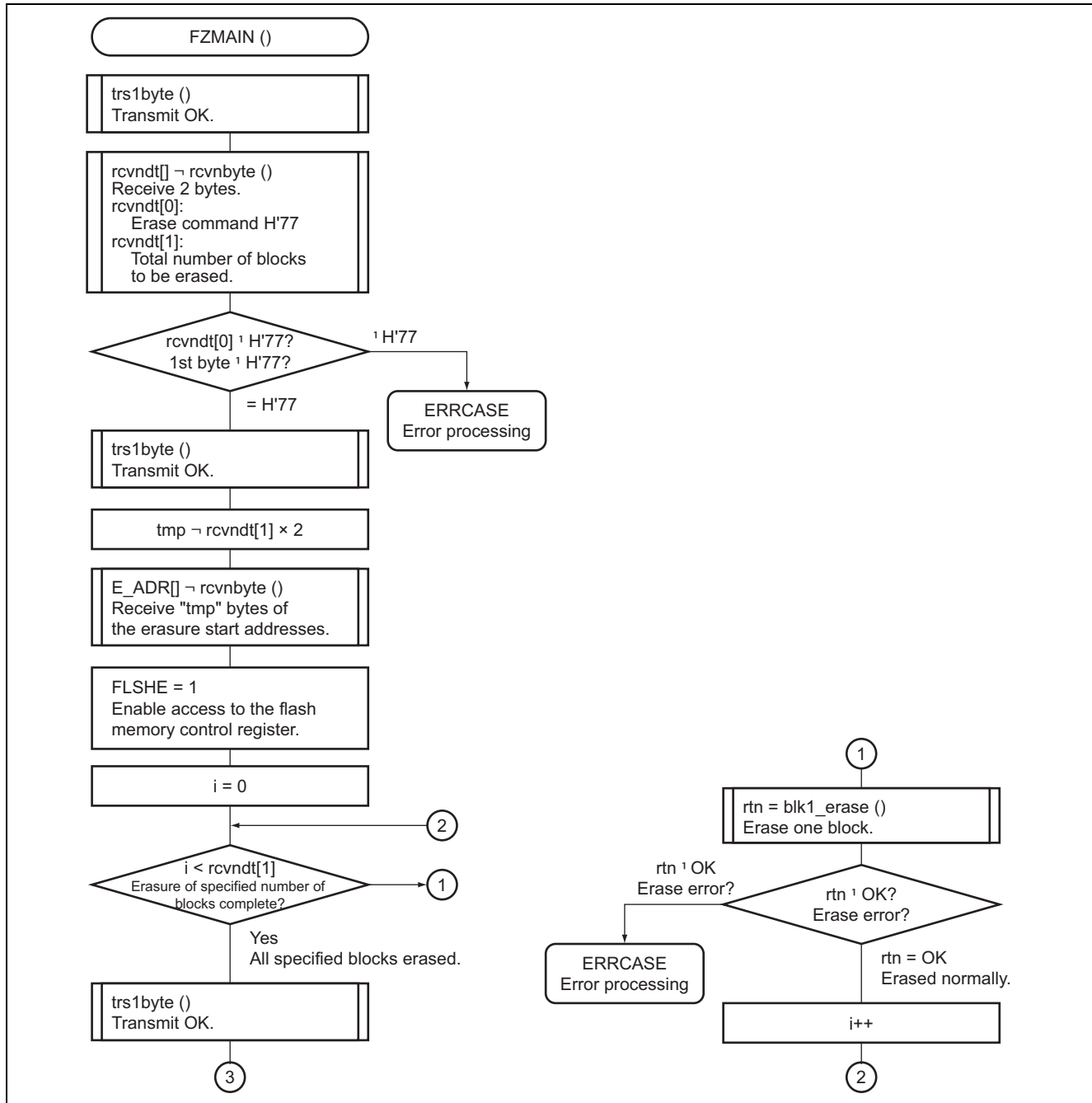
- TCWD: Timer counter WD (Address: H'FFC1)
  - Function: 8-bit counter which takes the  $\phi/8192$  clock as input
  - Setting value: H'FF
- TMWD: Timer mode register WD (Address H'FFC2)

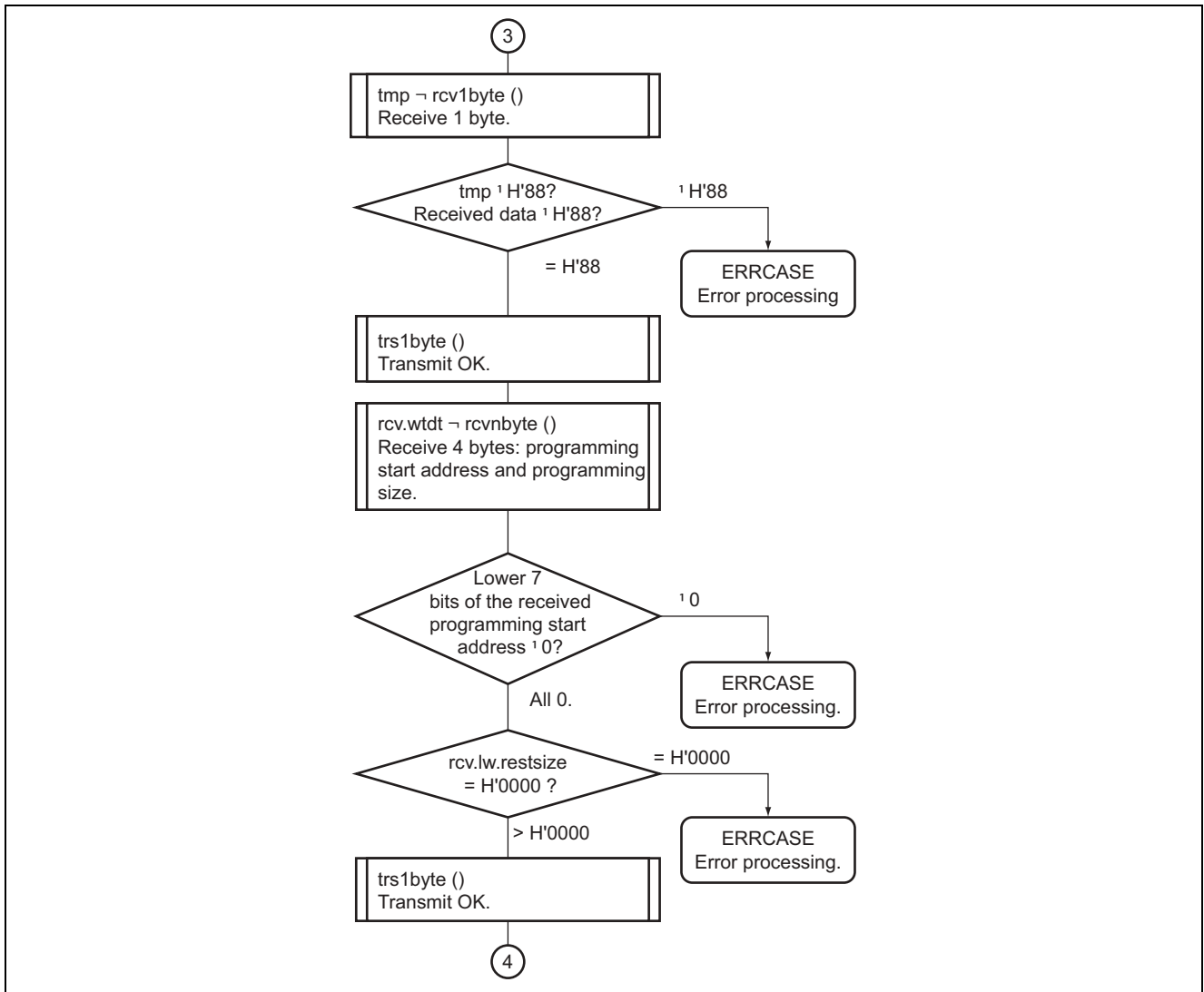
Bit	Bit Name	Setting	Description
3	CKS3	1	Clock Select 3 to 0
2	CKS2	1	When CKS3 to CKS0 are set to B'1111, $\phi/8192$ is selected as the input clock for TCWD.
1	CKS1	1	
0	CKS0	1	

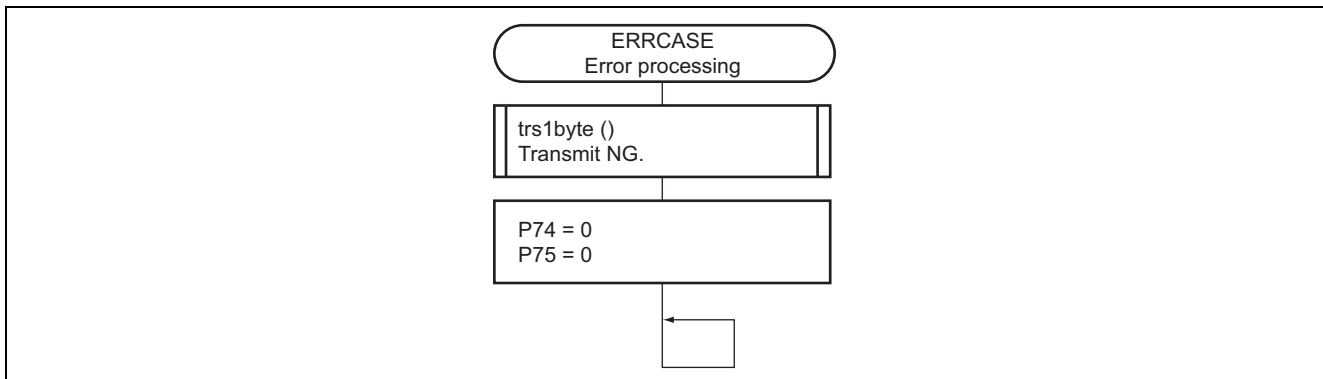
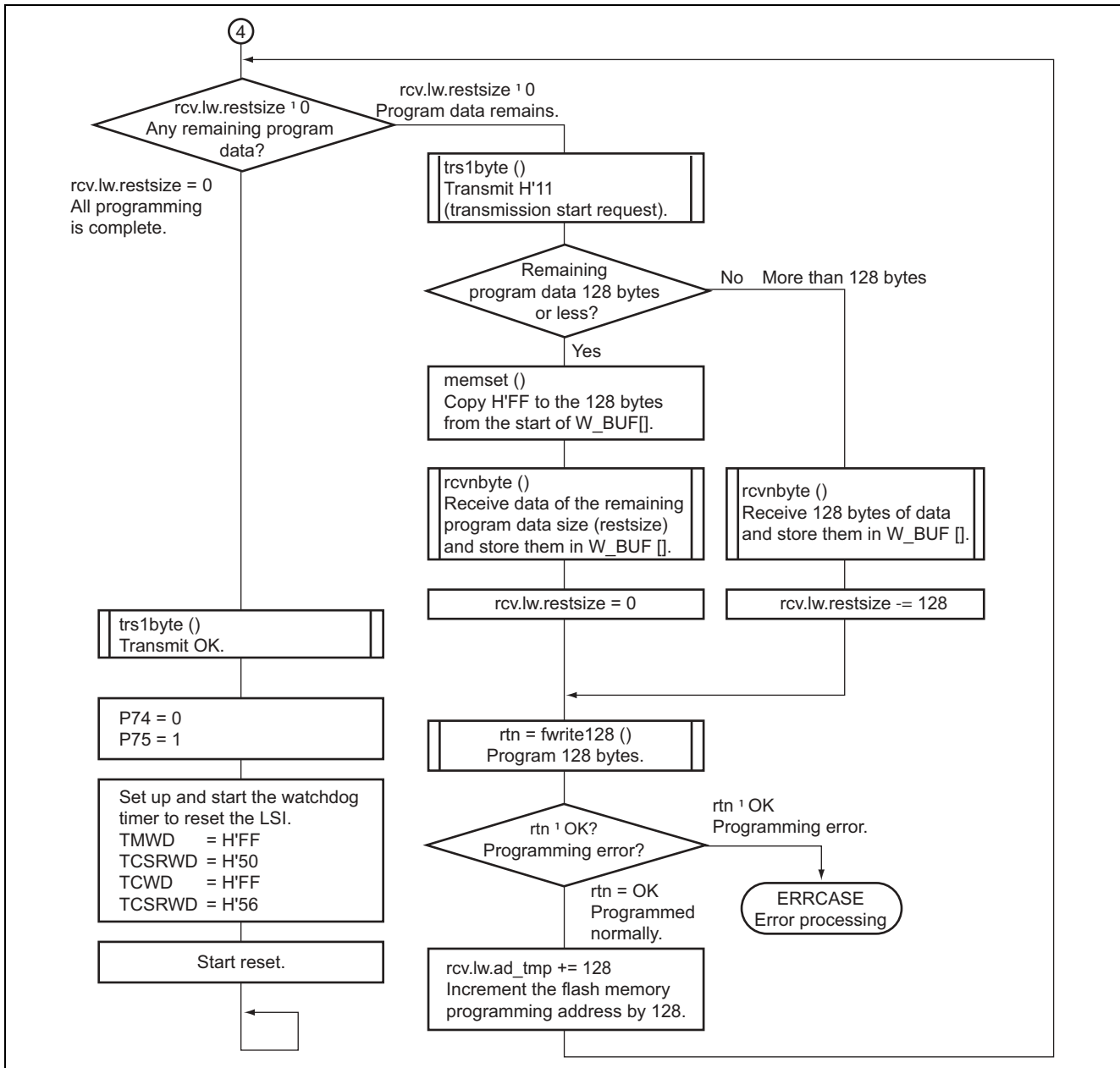
- PDR7: Port data register 7 (Address: H'FFDA)

Bit	Bit Name	Setting	Description
5	P75	Undefined	Port 75 0: The P75 pin is low. 1: The P75 pin is high.
4	P74	0	Port 74 0: The P74 pin is low. 1: The P74 pin is high.

### (3) Flowchart







## 6.5.2 blk1\_erase() Function

### (1) Module Specifications

- Functional summary
  - Determines the target erase block number from the erase start address.
  - Erases the specified block of flash memory.

**Table 13 Module Specifications**

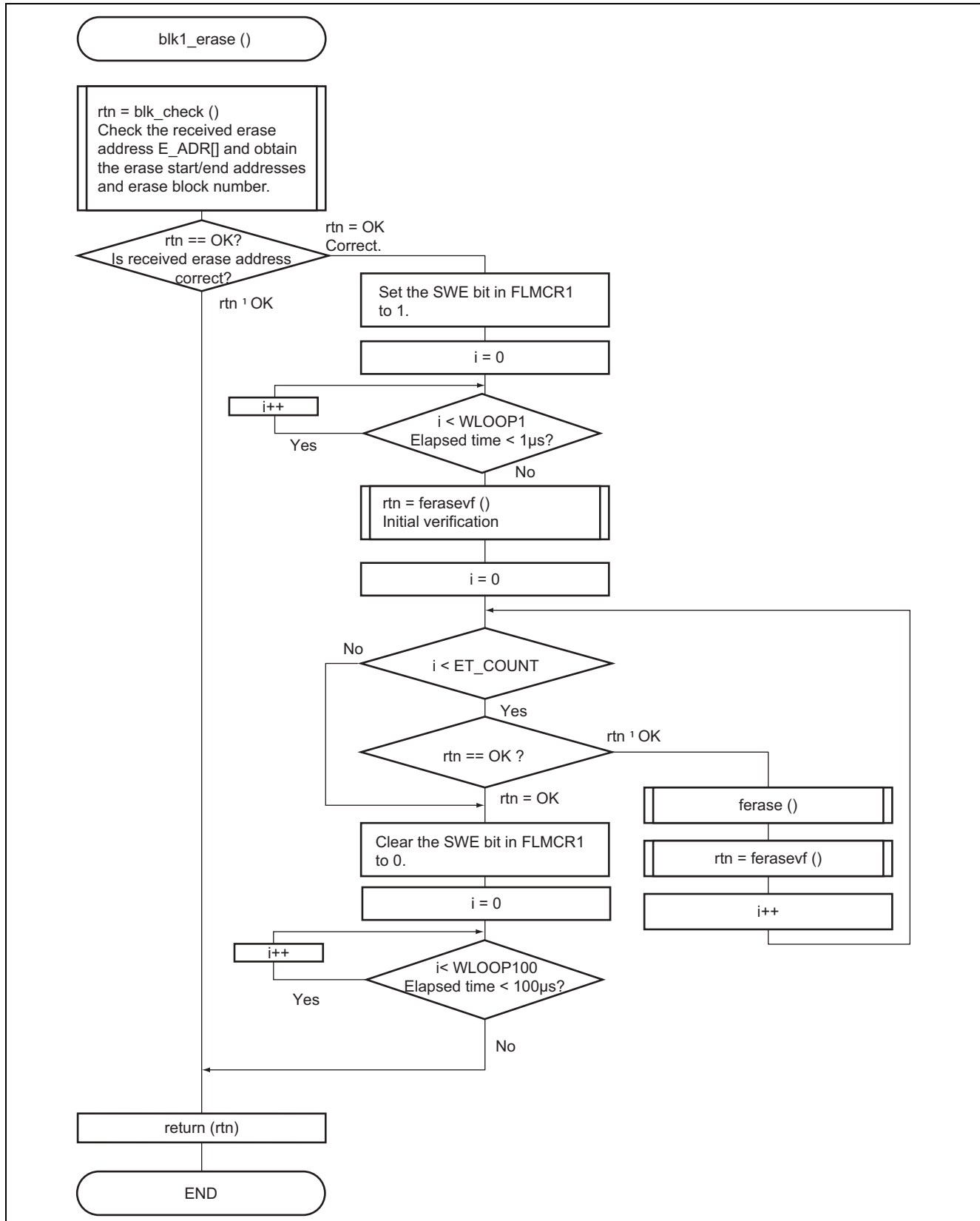
	Type	Variable Name	Description
Argument	unsigned short	ers_ad	Erase start address
	unsigned char	ET_COUNT	Maximum number of erasures
Return value	char	—	Result flag (OK = H'00, NG = H'01)

### (2) Internal Register

- FLMCR1: Flash memory control register 1 (Address: H'FF90)

Bit	Bit Name	Setting	Description
6	SWE	1	Software Write Enable 0: Disables flash memory programming/erasure. 1: Enables flash memory programming/erasure.

### (3) Flowchart



### 6.5.3 blk\_check() Function

#### (1) Module Specifications

- Functional summary
  - Determines the target erase block number from the erase start address.
  - Performs comparison with BLOCKADR[] to find out if the received erase start address value is correct, and returns the result flag, erase start address, erase end address, and block number.

**Table 14 Module Specifications**

	Type	Variable Name	Contents
Argument	unsigned short	eck_ad	Erase start address
	unsigned short	*eck_st	Erase start address after verification
	unsigned short	*eck_ed	Erase end address after verification
	unsigned char	*blk_no	Target erase block number
Return value	char	—	Result flag (OK = H'00; NG = H'01)

#### (2) Internal Registers

None

#### (3) Global Variables

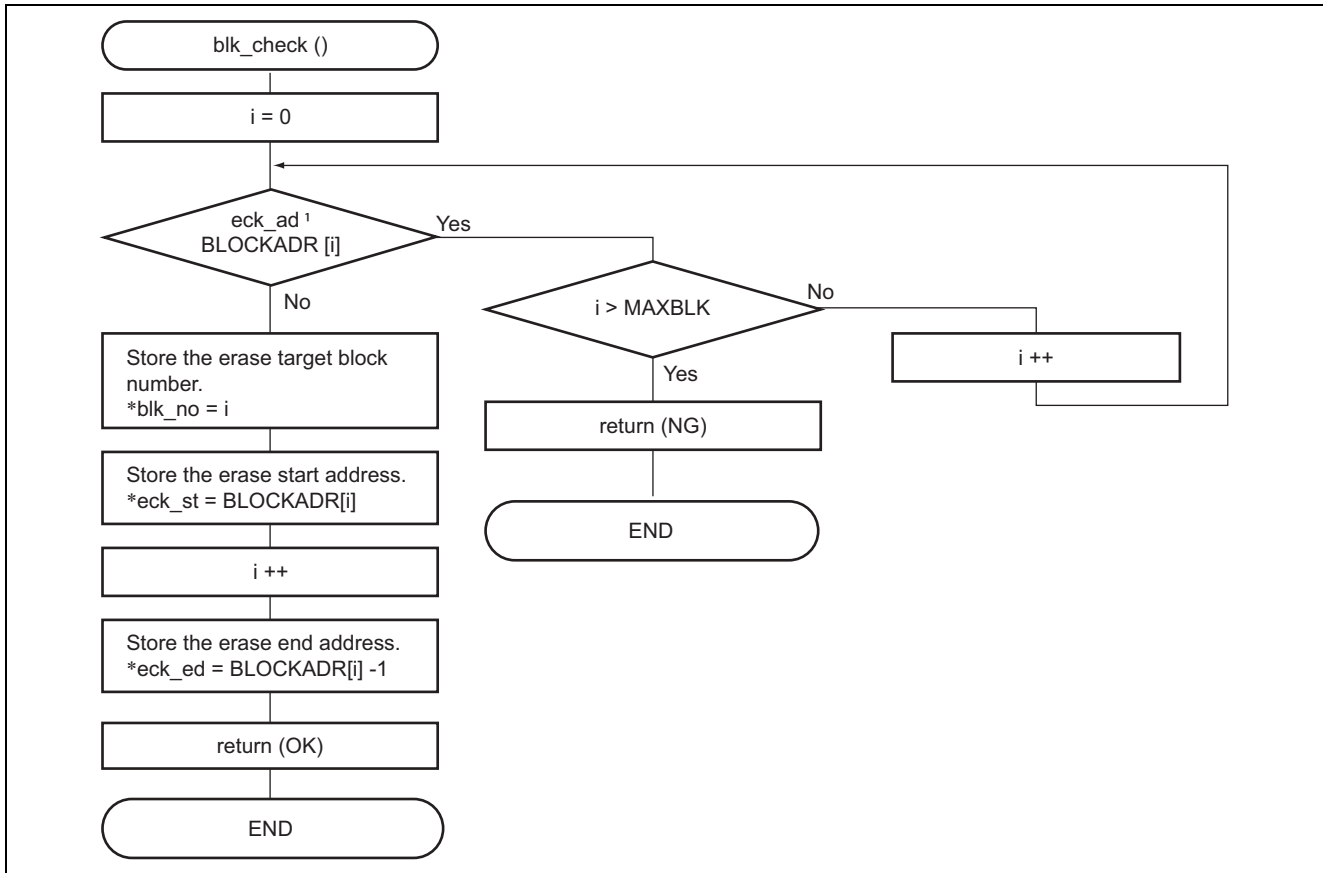
- BLOCKADR[]: Stores the start addresses of blocks in flash memory.

```

unsigned short BLOCKADR[6] = {
    0x0000, /* Erase Block Address */
    0x0400, /* EB0 1KBYTE */
    0x0800, /* EB1 1KBYTE */
    0x0c00, /* EB2 1KBYTE */
    0x1000, /* EB3 1KBYTE */
    0x1000, /* EB4 28KBYTE */
    0x8000, /* End Block Address */
};

```

(4) Flowchart



### 6.5.4 ferase() Function

#### (1) Module Specifications

- Functional summary  
— Erases the specified block of flash memory

**Table 15 Module Specifications**

	Type	Variable Name	Description
Argument	unsigned char	e_blk_no	Target erase block number

#### (2) Internal Registers

- FLMCR1: Flash memory control register 1 (Address: H'FF90)

Bit	Bit Name	Setting	Description
5	ESU	1	Erase Setup 0: Cancels an erase setup state. 1: Enters an erase setup state.
1	E	1	Erase 0: Cancels erase mode. 1: Erase mode is entered if SWE = 1 and ESU = 1.

- EBR1: Block specification register 1 (Address: H'FF93)

Bit	Bit Name	Setting	Description
4	EB4	0	When this bit is set to 1, the 28 kbytes from H'1000 to H'7FFF are specified to be erased.
3	EB3	0	When this bit is set to 1, the 1 kbytes from H'0C00 to H'0FFF are specified to be erased.
2	EB2	0	When this bit is set to 1, the 1 kbytes from H'0800 to H'0BFF are specified to be erased.
1	EB1	0	When this bit is set to 1, the 1 kbytes from H'0400 to H'07FF are specified to be erased.
0	EB0	0	When this bit is set to 1, the 1 kbytes from H'0000 to H'03FF are specified to be erased.

Note: This register specifies the erase block of flash memory. When the SWE bit in FLMCR1 is 0, EBR1 is initialized to H'00. Multiple bits of this register should not be set to 1 at a time. When set, EBR1 is cleared to 0 automatically.

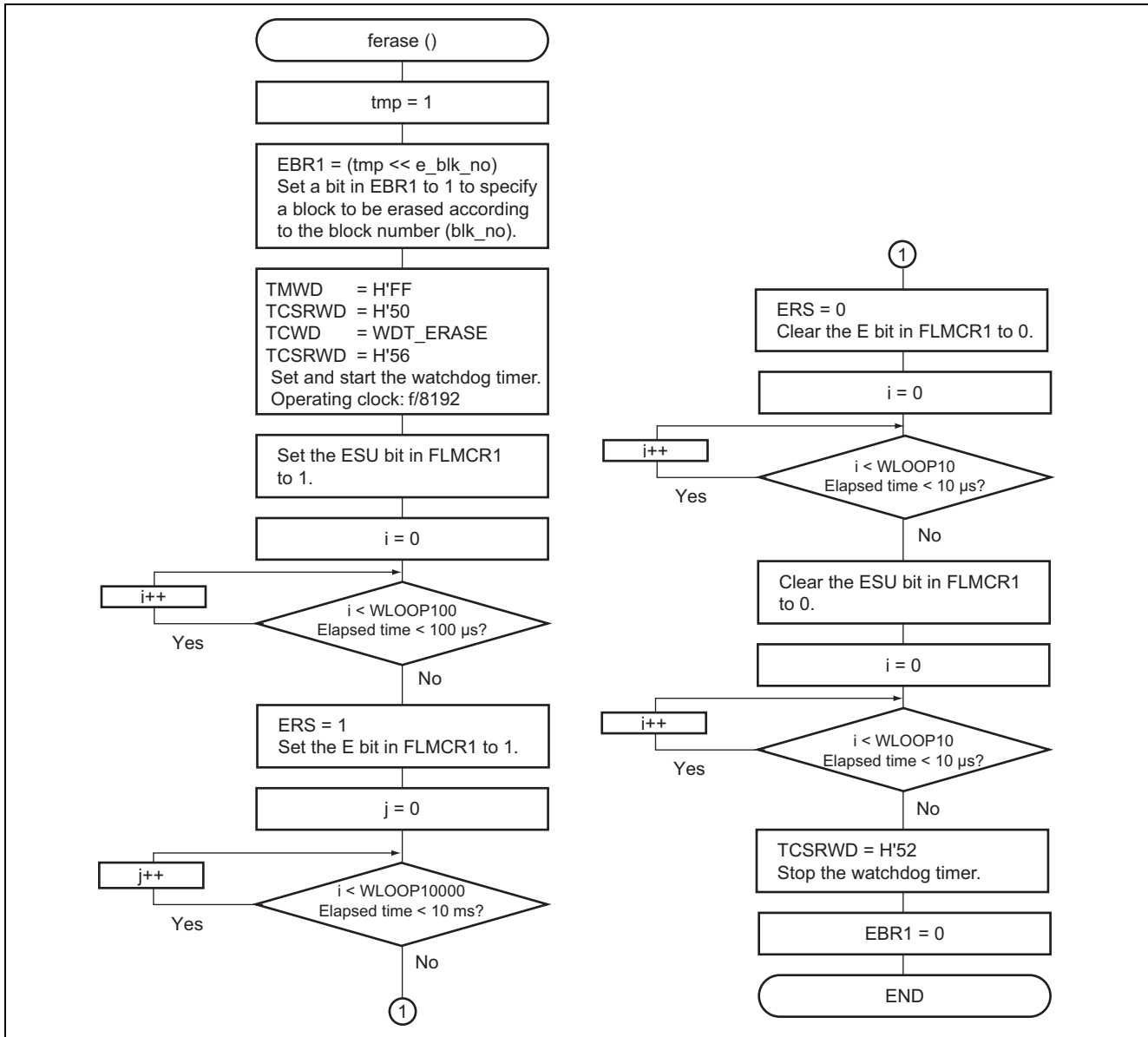
- TCSRWD: Timer control/status register WD (Address: H'FFC0)

Bit	Bit Name	Setting	Description
7	B6WI	0	Bit 6 Write Disable 0: Enables writing to bit 6 in TCSRWD. 1: Disables writing to bit 6 in TCSRWD.
6	TCWE	1	Timer Counter WD Write Enable 0: Disables writing 8-bit data to TCWD. 1: Enables writing 8-bit data to TCWD.
5	B4WI	0	Bit 4 Write Disable 0: Enables writing to bit 4 in TCSRWD. 1: Disables writing to bit 4 in TCSRWD.
4	TCSRWE	1	Timer Control/Status Register WD Write Enable 0: Disables writing to bit 2 and bit 0 in TCSRWD. 1: Enables writing to bit 2 and bit 0 in TCSRWD.
3	B2WI	0	Bit 2 Write Disable 0: Enables writing to bit 2 in TCSRWD. 1: Disables writing to bit 2 in TCSRWD.
2	WDON	0	Watchdog Timer On 0: Disables watchdog timer operation. 1: Enables watchdog timer operation.
1	B0WI	0	Bit 0 Write Disable 0: Enables writing to bit 0 in TCSRWD. 1: Disables writing to bit 0 in TCSRWD.
0	WRST	0	Watchdog Timer Reset 0: Indicates that TCWD has not overflowed and an internal reset signal has not been generated. 1: Indicates that TCWD has overflowed and an internal reset signal has been generated.

- TCWD: Timer counter WD (Address: H'FFC1)
  - Function: 8-bit counter which takes the  $\phi/8192$  clock as input
  - Setting value: WDT\_ERASE (H'A0)
- TMWD: Timer mode register WD (Address H'FFC2)

Bit	Bit Name	Setting	Description
3	CKS3	1	Clock Select 3 to 0
2	CKS2	1	When CKS3 to CKS0 are set to B'1111, $\phi/8192$ is selected as the input clock for TCWD.
1	CKS1	1	
0	CKS0	1	

### (3) Flowchart



### 6.5.5 ferasevf() Function

#### (1) Module Specifications

- Functional summary:
  - Verifies that the specified block in the flash memory has been erased.

**Table 16 Module Specifications**

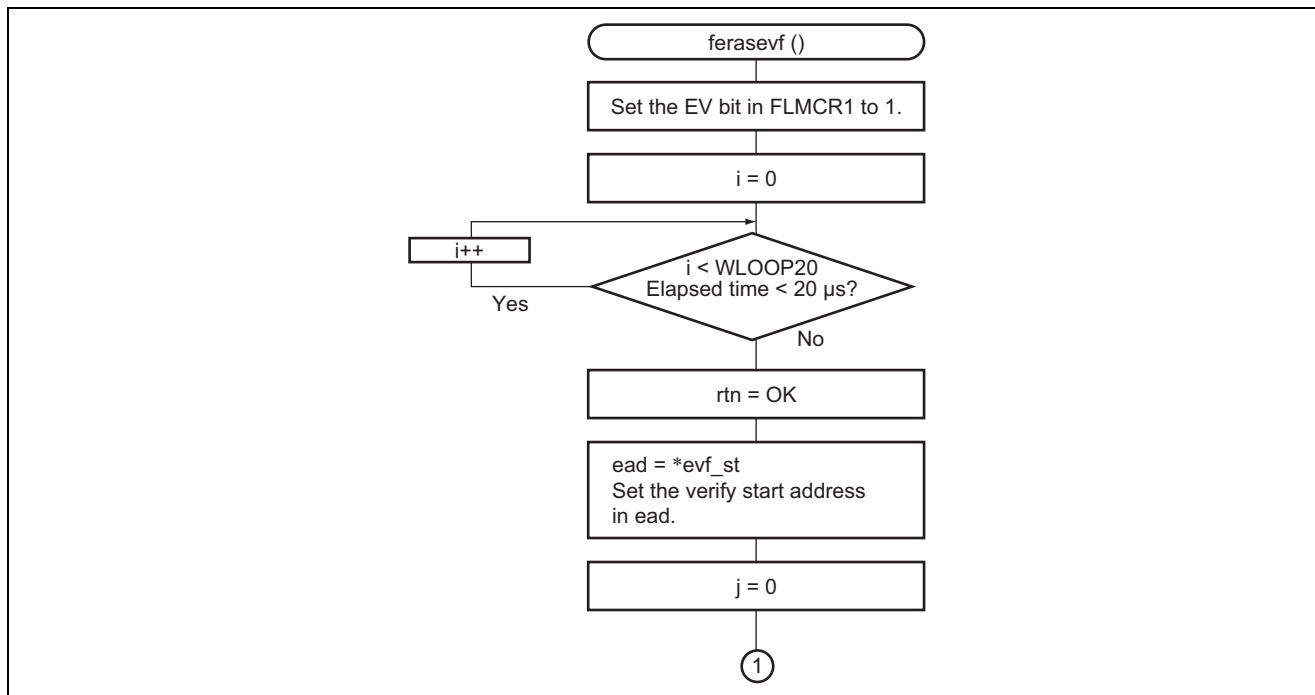
	Type	Variable Name	Description
Argument	unsigned short	evf_st	Erase start address
	unsigned short	evf_ed	Erase end address
Return value	char	—	Result flag (OK = H'00; NG = H'01)

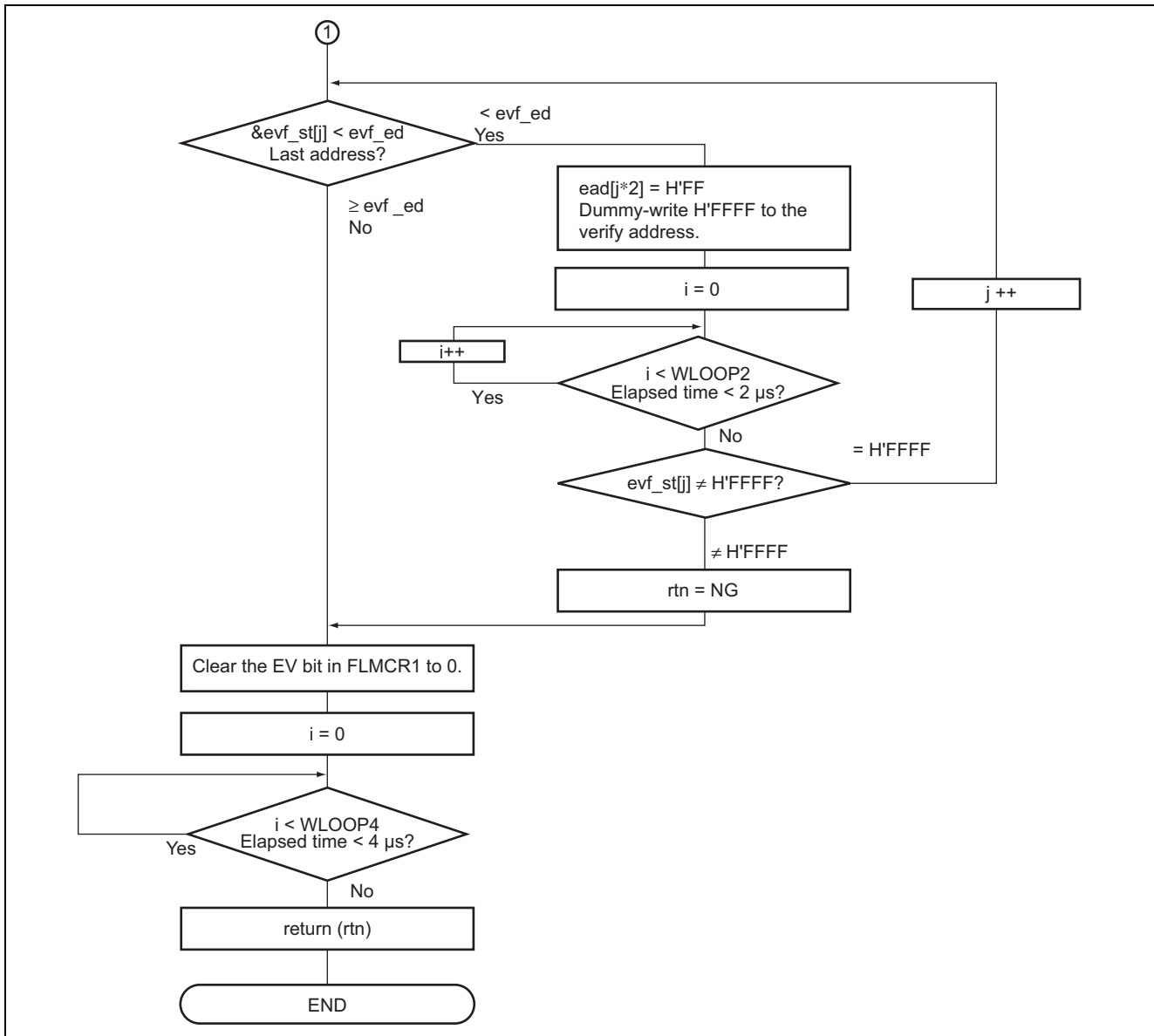
#### (2) Internal Registers

- FLMCR1: Flash memory control register 1 (Address: H'FF90)

Bit	Bit Name	Setting	Description
3	EV	1	Erase Verify 0: Cancels erase-verify mode. 1: Enters erase-verify mode.

#### (3) Flowchart





### 6.5.6 fwrite128() Function

#### (1) Module Specifications

- Functional summary  
— Programs 128 bytes and performs verification.

**Table 17 Module Specifications**

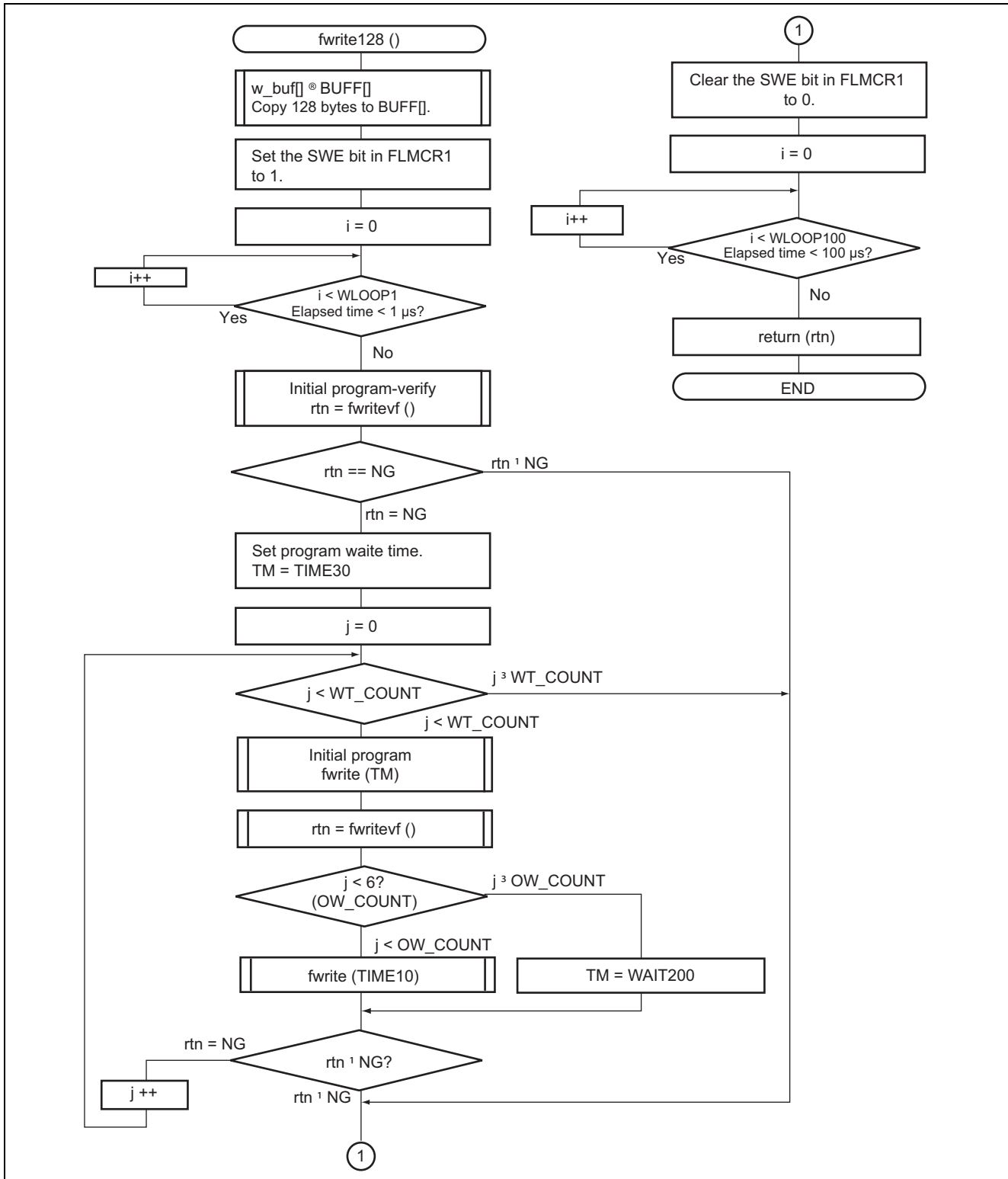
	Type	Variable Name	Description
Argument	unsigned char	*wt_buf	128 bytes of program data
	unsigned char	*wt_adr	Programming address
	unsigned short	WT_COUNT	Maximum number of programming operations
Return value	char	—	Result flag (OK = H'00; NG = H'01)

#### (2) Internal Register

- FLMCR1: Flash memory control register 1 (Address: H'FF90)

Bit	Bit Name	Setting	Description
6	SWE	1	Software Write Enable 0: Disables flash memory programming/erasure. 1: Enables flash memory programming/erasure.

### (3) Flowchart



### 6.5.7 fwrite() Function

#### (1) Module Specifications

- Functional summary
  - Writes addresses for programming.

**Table 18 Module Specifications**

	Type	Variable Name	Description
Argument	unsigned char	*buf	Program start address (reprogramming data or additional programming data)
	unsigned char	*w_adr	Program address
	unsigned short	ptime	P-bit setting time (10 $\mu$ s, 30 $\mu$ s, or 2000 $\mu$ s)

#### (2) Internal Registers

- FLMCR1: Flash memory control register 1 (Address: H'FF90)

Bit	Bit Name	Setting	Description
4	PSU	1	Program Setup 0: Cancels program setup state. 1: Enters program setup state.
0	P	1	Program 0: Cancels program mode. 1: Program mode is entered if SWE = 1 and PSU = 1.

- TCSRWD: Timer control/status register WD (Address: H'FFC0)

Bit	Bit Name	Setting	Description
7	B6WI	0	Bit 6 Write Disable 0: Enables writing to bit 6 in TCSRWD. 1: Disables writing to bit 6 in TCSRWD.
6	TCWE	1	Timer Counter WD Write Enable 0: Disables writing 8-bit data to TCWD. 1: Enables writing 8-bit data to TCWD.
5	B4WI	0	Bit 4 Write Disable 0: Enables writing to bit 4 in TCSRWD. 1: Disables writing to bit 4 in TCSRWD.
4	TCSRWE	1	Timer Control/Status Register WD Write Enable 0: Disables writing to bit 2 and bit 0 in TCSRWD. 1: Enables writing to bit 2 and bit 0 in TCSRWD.
3	B2WI	0	Bit 2 Write Disable 0: Enables writing to bit 2 in TCSRWD. 1: Disables writing to bit 2 in TCSRWD.
2	WDON	0	Watchdog Timer On 0: Disables watchdog timer operation. 1: Enables watchdog timer operation.

Bit	Bit Name	Setting	Description
1	BOWI	0	Bit 0 Write Disable 0: Enables writing to bit 0 in TCSRWD. 1: Disables writing to bit 0 in TCSRWD.
0	WRST	0	Watchdog Timer Reset 0: Indicates that TCWD has not overflowed and an internal reset signal has not been generated. 1: Indicates that TCWD has overflowed and an internal reset signal has been generated.

- TCWD: Timer counter WD (Address: H'FFC1)
  - Function: 8-bit counter which takes the  $\phi/8192$  clock as input
  - Setting value: WDT\_WRITE (H'F0)
- TMWD: Timer mode register WD (Address H'FFC2)

Bit	Bit Name	Setting	Description
3	CKS3	1	Clock Select 3 to 0
2	CKS2	1	When CKS3 to CKS0 are set to B'1111, $\phi/8192$ is selected as the input clock for TCWD.
1	CKS1	1	
0	CKS0	1	



### 6.5.8 fwritevf() Function

#### (1) Module Specifications

- Functional summary
  - Verifies the specified address and creates reprogramming data.

**Table 19 Module Specifications**

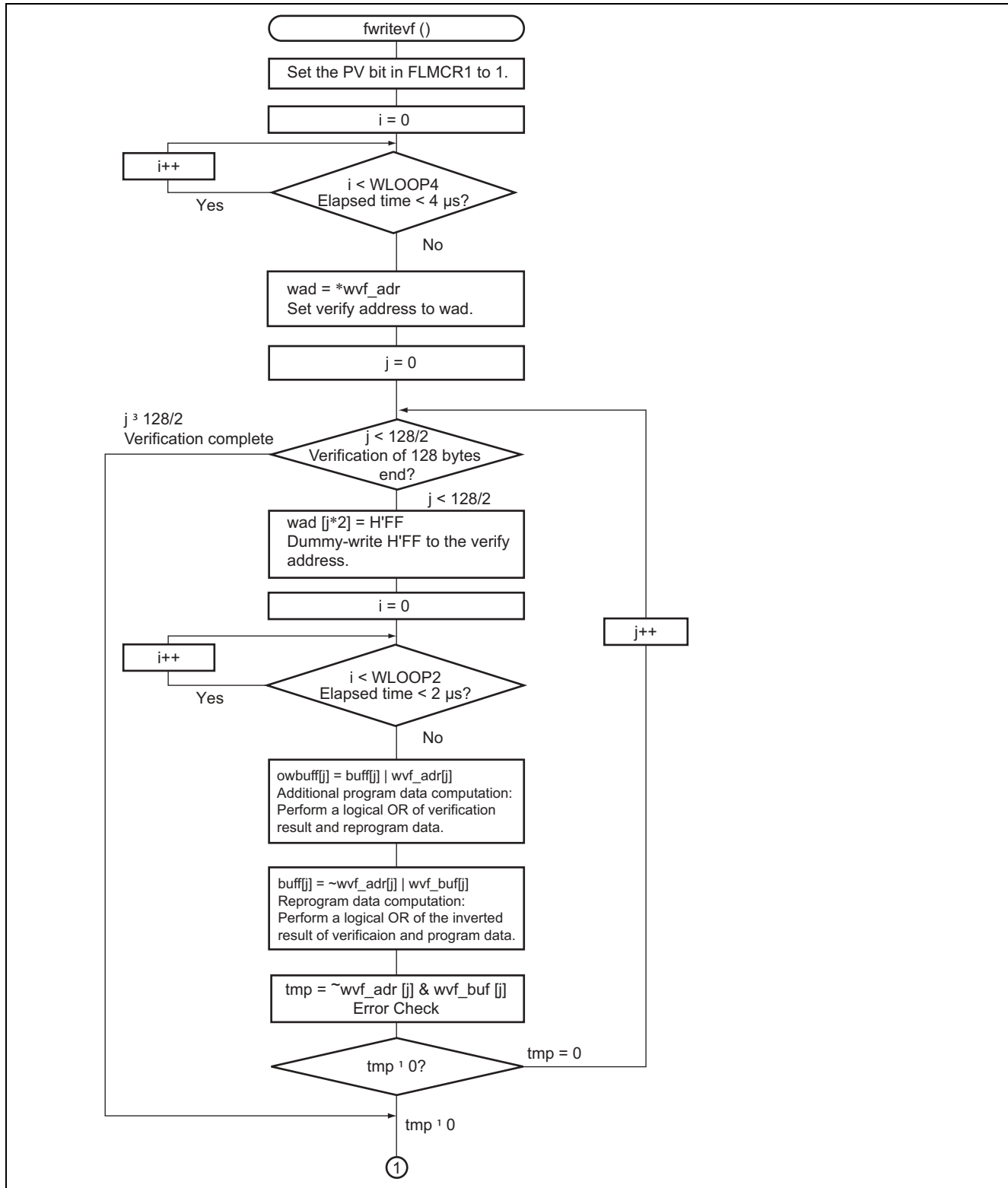
	Type	Variable Name	Contents
Argument	unsigned short	*owbuff	128 bytes of additional programming data
	unsigned short	*buff	128 bytes of reprogramming data
	unsigned short	*wvf_buf	128 bytes of programming data
	unsigned short	*wvf_adr	Program address
Return value	char	—	Result flag (OK = H'00, NG = H'01, or WNG = H'02)

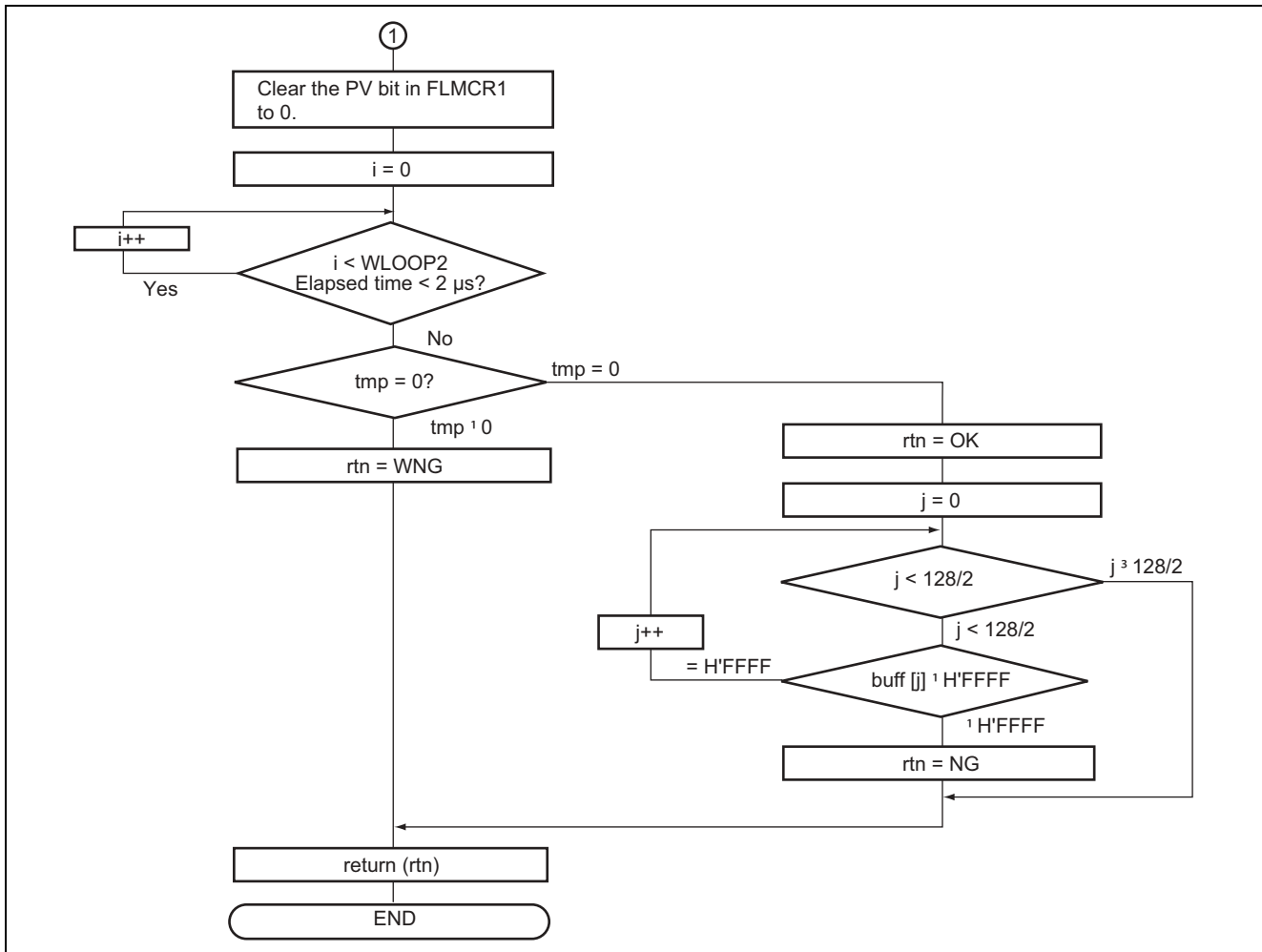
#### (2) Internal Registers

- FLMCR1: Flash memory control register 1 (Address: H'FF90)

Bit	Bit Name	Setting	Description
2	PV	1	Program Verify 0: Cancels program-verify mode. 1: Enters program-verify mode.

### (3) Flowchart





## 7. Asynchronous Serial Communication Program

### 7.1 Hierarchical Structure

The asynchronous serial communication program performs processing to communicate with the master device.

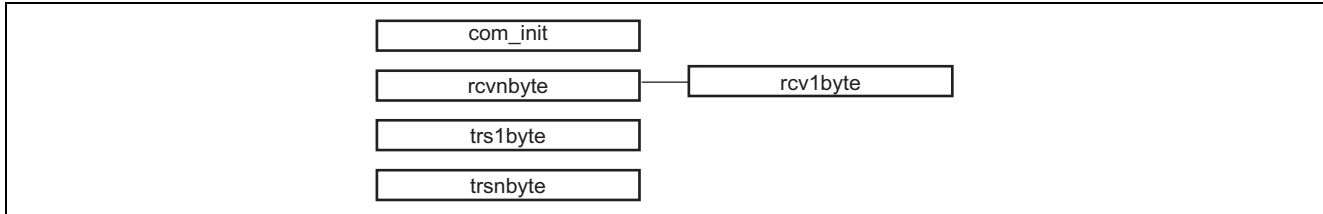


Figure 19 Asynchronous Serial Communication Program

### 7.2 List of Functions

Table 20 Asynchronous Serial Communication Program Functions

Function Name	Summary
com_init	Initializes asynchronous serial communication settings.
rcv1byte	Receives one byte of data.
rcvnbyte	Receives n bytes of data.
trs1byte	Transmits one byte of data.
trsnbyte	Transmits n bytes of data.

## 7.3 Modules

### 7.3.1 com\_init() Function

#### (1) Module Specifications

- Functional summary  
— Initializes asynchronous serial communication settings.

**Table 21 Module Specifications**

Argument	Type	Variable Name	Description
	None	None	None

#### (2) Internal Registers

- SMR: Serial mode register (Address: H'FFA8)

Bit	Bit Name	Setting	Description
7	COM	0	Communication Mode 0: Sets communication mode to asynchronous mode. 1: Sets communication mode to synchronous mode.
6	CHR	0	Character Length 0: Sets data length in asynchronous mode to 8 bits. 1: Sets data length in asynchronous mode to 7 bits.
5	PE	0	Parity Enable 0: Disables parity bit addition and check during transmission in asynchronous mode. 1: Enables parity bit addition and check during transmission in asynchronous mode.
4	PM	0	Parity Mode 0: Selects even parity for parity addition and check. 1: Selects odd parity for parity addition and check.
3	STOP	0	Stop Bit Length 0: Sets stop bit length to 1 bit in asynchronous mode. 1: Sets stop bit length to 2 bits in asynchronous mode.
2	MP	0	Multiprocessor Mode 0: Disables multiprocessor communication functions. 1: Enables multiprocessor communication functions.
1	CKS1	0	Clock Select 1, 0
0	CKS0	0	When CKS1 = 0 and CKS0 = 0, clock source for the on-chip baud rate generator is set to $\phi$ .

- BRR: Bit rate register (Address: H'FFA9)  
— Functions: When BRR = H'12, the transmit bit rate that is in accordance with the baud rate generator's operating clock selected by CKS1 and CKS0 in SMR is set to 38,400 bps.  
— Setting value: H'12

- SCR3: Serial control register 3 (Address: H'FFAA)

Bit	Bit Name	Setting	Description
5	TE	0	Transmit Enable 0: Disables transmission. 1: Enables transmission.
4	RE	0	Receive Enable 0: Disables reception. 1: Enables reception.
1	CKE1	0	Clock Enable 1, 0
0	CKE0	0	When CKE1 = 0 and CKE0 = 0, internal clock is used as the clock source in asynchronous mode and the SCK32 pin functions as an I/O port.

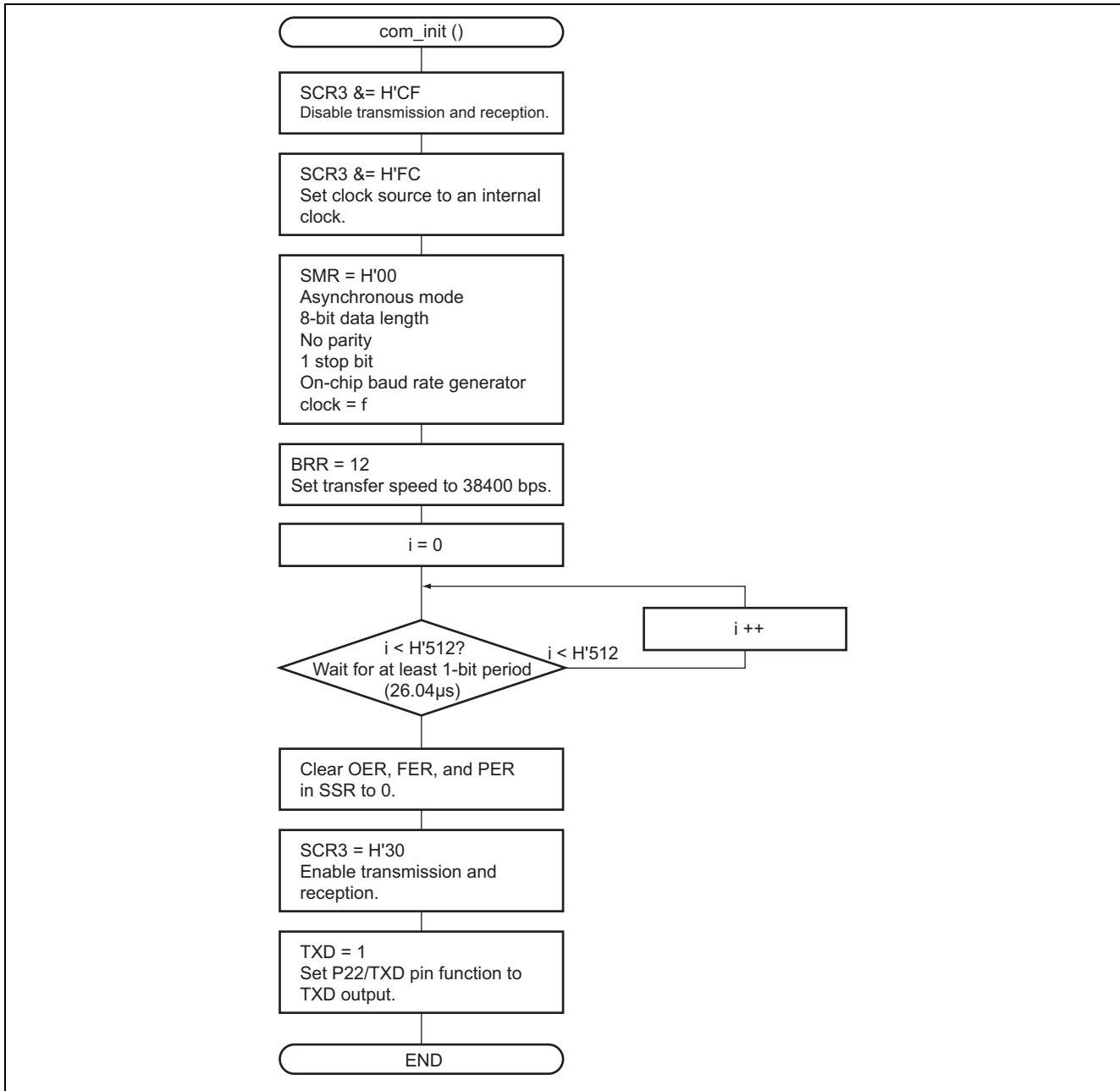
- SSR: Serial status register (Address: H'FFAC)

Bit	Bit Name	Setting	Description
7	TDRE	Undefined	Transmit Data Register Empty 0: Indicates that transmit data written to TDR has not been transferred to TSR. 1: Indicates that transmit data has not been written to TDR or transmit data written to TDR has been transferred to TSR.
6	RDRF	Undefined	Receive Data Register Full 0: Indicates that receive data has not been stored in RDR. 1: Indicates that receive data has been stored in RDR.
5	OER	0	Overrun Error 0: Indicates that reception is in progress or complete. 1: Indicates that an overrun error occurred during reception.
4	FER	0	Framing Error 0: Indicates that reception is in progress or complete. 1: Indicates that a framing error occurred during reception.
3	PER	0	Parity Error 0: Indicates that reception is in progress or complete. 1: Indicates that a parity error occurred during reception.
2	TEND	Undefined	Transmit End 0: Indicates that transmission is in progress. 1: Indicates that transmission is complete.

- PMR1: Port mode register (Address: H'FFEC)

Bit	Bit Name	Setting	Description
1	TXD	1	P22/TXD Pin Function Select 0: The P22/TXD pin functions as the P22 pin. 1: The P22/TXD pin functions as the TXD output pin.

### (3) Flowchart



### 7.3.2 rcv1byte() Function

#### (1) Module Specifications

- Functional summary  
— Receives one byte of asynchronous serial data.

**Table 22 Module Specifications**

	Type	Variable Name	Contents
Argument	None	None	None
Return value	unsigned char	—	One byte of received data

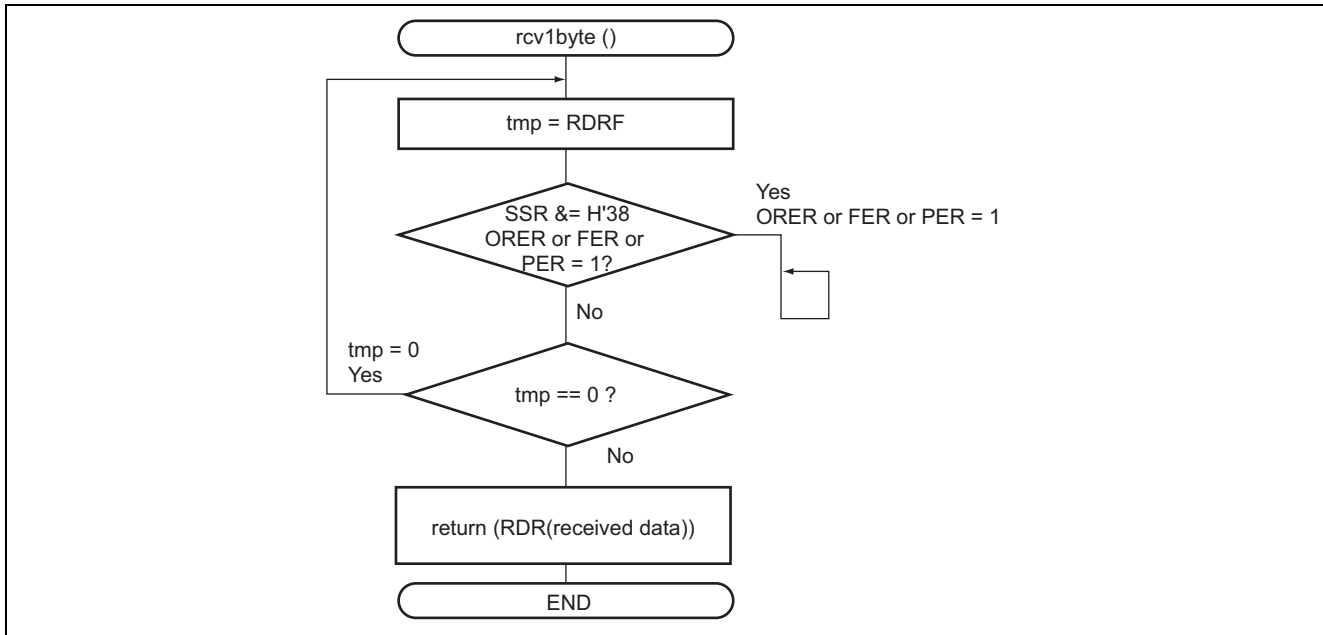
#### (2) Internal Registers

- SSR: Serial status register (Address: H'FFAC)

Bit	Bit Name	Setting	Description
6	RDRF	Undefined	Receive Data Register Full 0: Indicates that receive data has not been stored in RDR. 1: Indicates that receive data has been stored in RDR.
5	OER	Undefined	Overrun Error 0: Indicates that reception is in progress or complete. 1: Indicates that an overrun error occurred during reception.
4	FER	Undefined	Framing Error 0: Indicates that reception is in progress or complete. 1: Indicates that a framing error occurred during reception.
3	PER	Undefined	Parity Error 0: Indicates that reception is in progress or complete. 1: Indicates that a parity error occurred during reception.

- RDR: Receive data register (Address: H'FFAD)  
— Function: 8-bit register which stores received data.  
— Setting value: Undefined

(3) Flowchart



### 7.3.3 rcvnbyte() Function

#### (1) Module Specifications

- Functional summary:
  - Receives n bytes of asynchronous serial data.

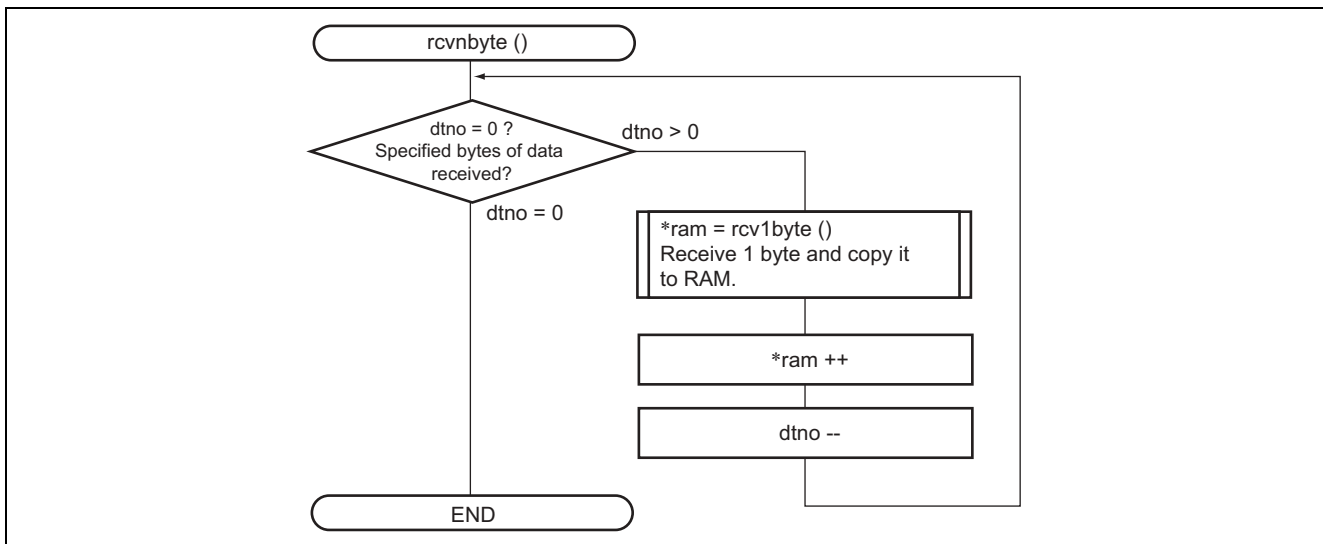
**Table 23 Module Specifications**

	Type	Variable Name	Description
Argument	unsigned char	*ram	Start address of RAM to store receive data.
	unsigned char	dtno	Number of bytes to be received

#### (2) Internal Registers

None

#### (3) Flowchart



### 7.3.4 trs1byte() Function

#### (1) Module Specifications

- Functional summary
  - Transmits 1 byte of asynchronous serial data.

**Table 24 Module Specifications**

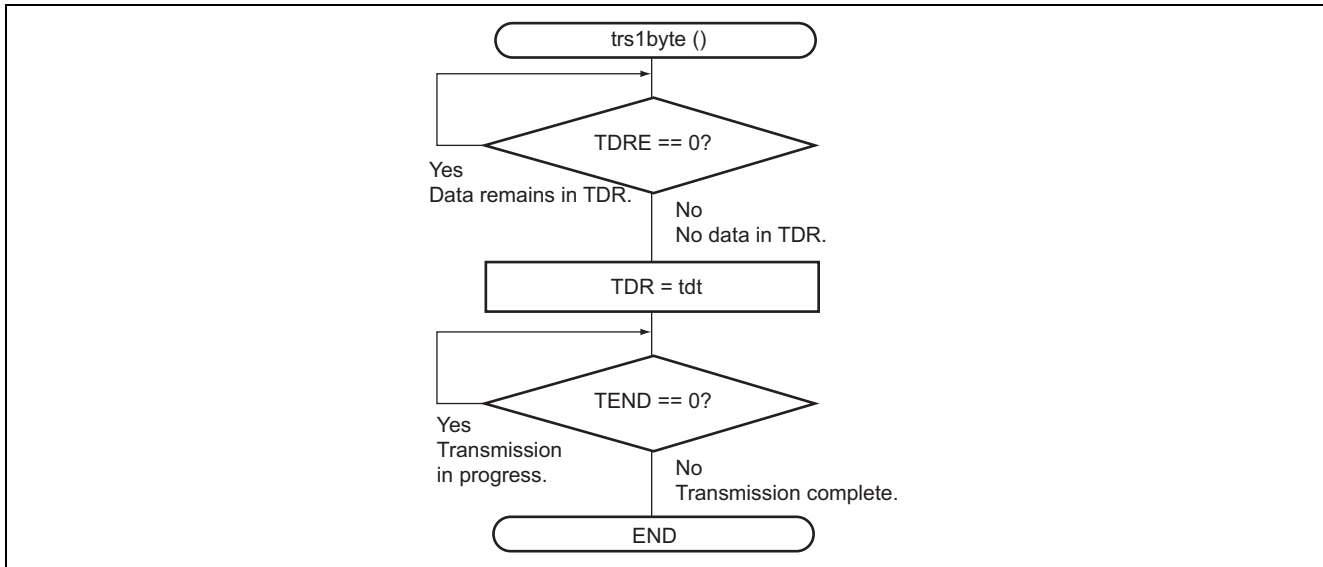
	Type	Variable Name	Contents
Argument	unsigned char	t dt	Byte transmit data

#### (2) Internal Registers

- TDR: Transmit data register (Address: H'FFAB)
  - Function: 8-bit register which stores transmit data.
  - Setting value: Undefined
- SSR: Serial status register (Address: H'FFAC)

Bit	Bit Name	Setting	Description
7	TDRE	Undefined	Transmit Data Register Empty 0: Indicates that transmit data written to TDR has not been transferred to TSR. 1: Indicates that transmit data has not been written to TDR or transmit data written to TDR has been transferred to TSR.
2	TEND	Undefined	Transmit End 0: Indicates that transmission is in progress. 1: Indicates that transmission is complete.

(3) **Flowchart**



### 7.3.5 trsnbyte() Function

#### (1) Module Specifications

- Functional summary:  
— Transmits n bytes of asynchronous serial data.

**Table 25 Module Specifications**

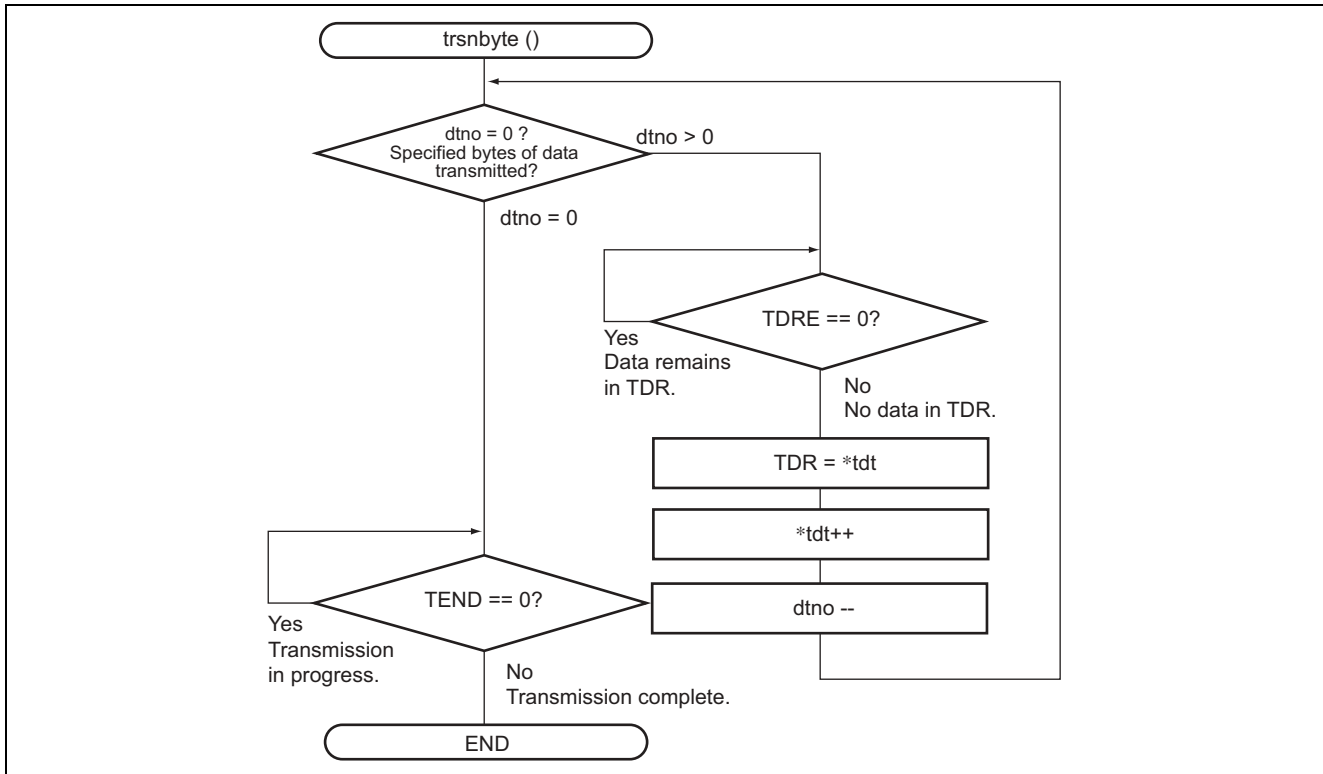
	Type	Variable Name	Contents
Argument	unsigned char	*tdt	Start address of transmit data
	unsigned char	dtno	Transmit data size

#### (2) Internal Registers

- TDR: Transmit data register (Address: H'FFAB)  
— Function: 8-bit register which stores transmit data.  
— Setting value: Undefined
- SSR: Serial status register (Address: H'FFAC)

Bit	Bit Name	Setting	Description
7	TDRE	Undefined	Transmit Data Register Empty 0: Indicates that transmit data written to TDR has not been transferred to TSR. 1: Indicates that transmit data has not been written to TDR or transmit data written to TDR has been transferred to TSR.
2	TEND	Undefined	Transmit End 0: Indicates that transmission is in progress. 1: Indicates that transmission is complete.

(3) **Flowchart**



## 8. Link Address Specifications

<b>Section Name</b>	<b>Address</b>
CV1	H'0000
P	H'0100
PASSCI	H'0400
DSMPL1	H'0800
DSMPL2	H'0C00
DSMPL3	H'0FF6
FZTAT, PFZTAT, DFZTAT, FZEND	H'1000
RAM, PRAM, DRAM	H'F780

### Revision Record

Rev.	Date	Description	
		Page	Summary
1.00	Jul.28.04	—	First edition issued

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